High-Voltage Power Discretes and Modules



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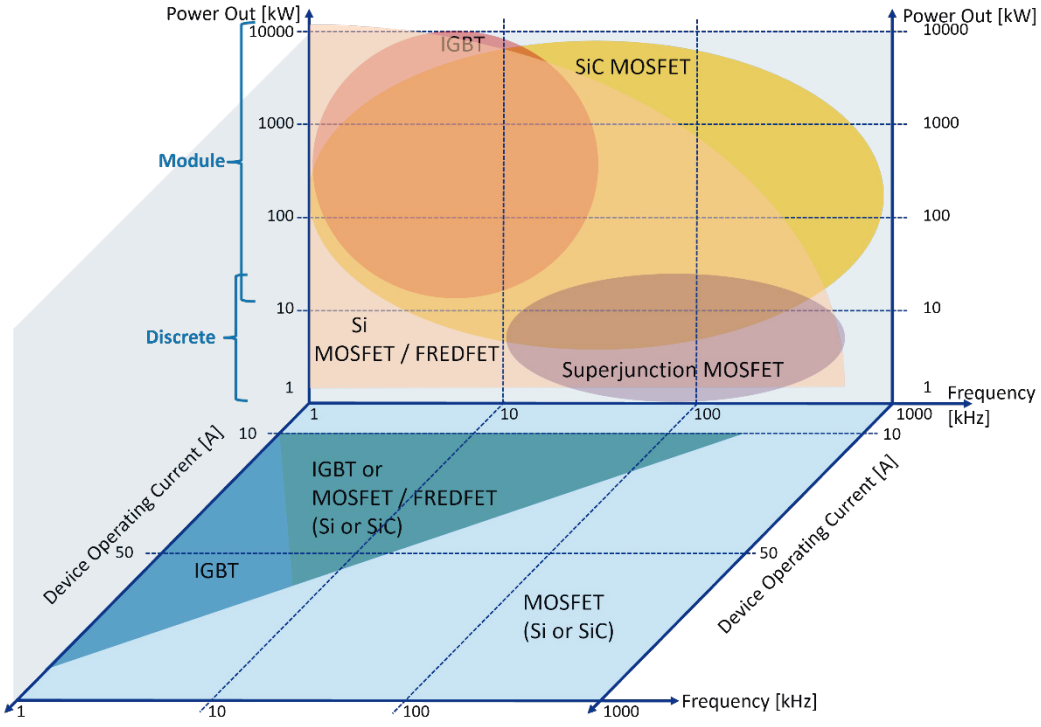
microchip.com/en-us/products/power-management/silicon-carbide

microchip.com/en-us/products/power-management/discretes

Power Discretes



We provide a broad portfolio of power discrete devices optimized for low-, medium-, and high-voltage applications requiring high efficiency, fast switching and robust thermal performance. Our portfolio supports a broad range of power conversion applications, with device architectures tailored to meet specific electrical and thermal design requirements.



These devices are engineered to deliver reliable operation under demanding electrical and thermal conditions and are available across a wide range of voltage classes, current ratings and package types—including surface-mount, through-hole, and advanced thermal packages. Whether the design goal is to minimize switching losses, improve thermal conductivity or withstand high-voltage transients, our discrete portfolio offers the electrical characteristics and form factors needed to meet stringent system requirements.

Our range of power discretes incorporates both conventional silicon and advanced wide-bandgap (WBG) semiconductor technologies, enabling higher power density, improved switching performance and reduced system size and cost in next-generation power electronics.

mSiC MOSFETs

Silicon Carbide (SiC) is the ideal technology for high-power applications above 650V, offering superior switching frequencies, higher efficiency, and reduced system size compared to traditional silicon-based solutions.

Our mSiC products and solutions deliver exceptional performance and reliability, enabling greater system efficiency traditional devices while significantly lowering total cost of ownership through reduced cooling requirements and downsized designs. With an oxide lifetime exceeding 100 years, a stable body diode, and best-in-class avalanche ruggedness, short-circuit capability and neutron immunity, our mSiC solutions ensure robust **system reliability, faster time to market, and reduced design risk**.

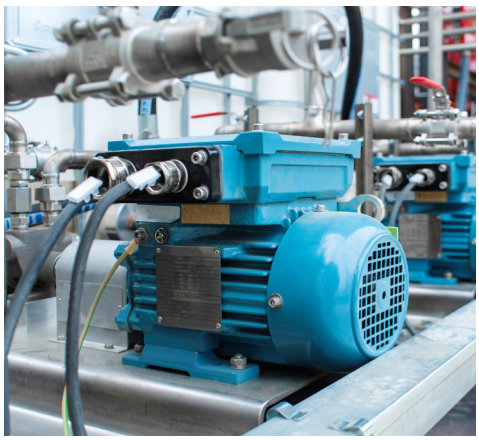
- **Extensive Product Range with Long-Term Availability –** We offer a broad portfolio of products with long-term availability, ensuring support for extended product lifecycles.
- **Versatile Solutions for Diverse Applications –** Our comprehensive and scalable product lineup caters to a wide array of applications and markets, providing flexibility and adaptability.
- **Standardized Packaging for Seamless Integration –** We provide industry-standard packaging options, making it easier to integrate our products into their existing systems.
- **Robust Development Tools and Support –** Benefit from our extensive development tools and system-level support, designed to streamline the design process and accelerate time-to-market.
- **Resilient Supply Chain with Multiple Sources –** Benefit from a diversified supply chain featuring multiple epi sources and fabs, ensuring uninterrupted product availability.

mSiC MOSFET Family Selection Guide

Item	Key Attributes	MA	MB	MC
Price	$/A	-	▼	▼
Compatibility	VGS(min)	18V	15V	15V
Performance	Switching Energy	Med	Low	Low
Performance	Integrated RG	No	No	Yes
Robustness	HV-H3TRB Capable	No	Yes	Yes
Performance	SCWT	+	+	+
Performance	RDS(on) vs Temp	++	+	+
Performance	Junction-to-Case Thermal Resistance	++	+	+
Robustness	Unclamped Inductive Switching (UIS)	+	+	+







mSiC MOSFETs

Part Number	Family (See Selection Guide - Page 4)	Voltage (V)	$R_{DS(on)}$ (mΩ)	Package Style
MSC090SMA070B	MA	700	90	TO-247
MSC090SMA070B4N	MA			TO-247-4 Notch
MSC090SMA070S	MA			TO-268
MSC090SMA070SC	MA			PSMT
MSC090SMA070SD	MA			TO-263-7 XL
MSC060SMA070B	MA		60	TO-247
MSC060SMA070B4	MA			TO-247-4
MSC060SMA070B4N	MA			TO-247-4 Notch
MSC060SMA070S	MA			TO-268
MSC060SMA070SC	MA			PSMT
MSC060SMA070SD	MA			TO-263-7 XL
MSC035SMA070B	MA		35	TO-247
MSC035SMA070B4	MA			TO-247-4
MSC035SMA070B4N	MA			TO-247-4 Notch
MSC035SMA070S	MA			TO-268
MSC035SMA070SD	MA			TO-263-7-XL
MSC015SMA070B	MA		15	TO-247
MSC015SMA070B4	MA			TO-247-4
MSC015SMA070B4N	MA			TO-247-4 Notch
MSC015SMA070S	MA			TO-268
MSC015SMA070SD	MA			TO-263-7-XL
MSC015SMA070J	MA			SOT-227
MSC360SMA120B	MA	1200	360	TO-247
MSC360SMA120B4N	MA			TO-247-4 Notch
MSC360SMA120S	MA			TO-268
MSC360SMA120SC	MA			PSMT
MSC360SMA120SD	MA			TO-263-7 XL
MSC180SMA120B	MA		180	TO-247
MSC180SMA120B4N	MA			TO-247-4 Notch
MSC180SMA120S	MA			TO-268
MSC180SMA120SC	MA			PSMT
MSC180SMA120SD	MA			TO-263-7 XL
MSC080SMA120B	MA		80	TO-247
MSC080SMA120B4	MA			TO-247-4
MSC080SMA120B4N	MA			TO-247-4 Notch
MSC080SMA120J	MA			SOT-227
MSC080SMA120S	MA			TO-268
MSC080SMA120SC	MA			PSMT
MSC080SMA120SD	MA			TO-263-7 XL
MSC080SMB120B	MB			TO-247
MSC080SMB120B4N	MB			TO-247-4 Notch
MSC080SMB120SD	MB			TO-263-7 XL
MSC080SMB120Q	MB			QDPAK
MSC060SMB120B	MB		60	TO-247
MSC060SMB120B4N	MB			TO-247-4 Notch
MSC060SMB120SD	MB			TO-263-7 XL
MSC060SMB120Q	MB			QDPAK
MSC045SMB120B4N	MB		45	TO-247-4 Notch
MSC045SMB120B	MB			TO-247
MSC045SMB120SD	MB			TO-263-7 XL
MSC045SMB120Q	MB			QDPAK

Auto-Qualified Part



TO-247 [B]



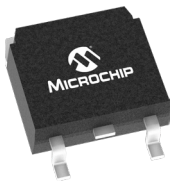
TO-247-4 [B4]



TO-247-4 Notch [B4N]



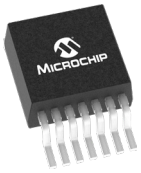
SOT-227 (Isolated Base) [J]



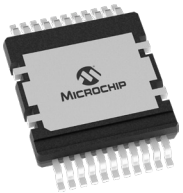
TO-268 (D3PAK) [S]



PSMT [SC]



TO-263-7 XL (D2PAK-7 XL) [SD]



QDPAK [Q]

mSiC MOSFETs (continued)

Part Number	Family (See Selection Guide - Page 4)	Voltage (V)	$R_{DS(on)}$ (mΩ)	Package Style
MSC040SMA120B 🚗	MA	1200	40	TO-247
MSC040SMA120B4	MA			TO-247-4
MSC040SMA120B4N 🚗	MA			TO-247-4 Notch
MSC040SMA120J	MA			SOT-227
MSC040SMA120S	MA			TO-268
MSC040SMA120SD	MA			TO-263-7-XL
MSC040SMB120SD 🚗	MB			TO-263-7 XL
MSC040SMB120B 🚗	MB			TO-247
MSC040SMB120B4N 🚗	MB			TO-247-4 Notch
MSC040SMB120Q 🚗	MB			QDPAK
MSC031SMC120B4N 🚗	MC		31	TO-247-4 Notch
MSC030SMB120B 🚗	MB		30	TO-247
MSC030SMB120B4N 🚗	MB			TO-247-4 Notch
MSC030SMB120Q 🚗	MB			QDPAK
MSC030SMB120SD 🚗	MB			TO-263-7 XL
MSC025SMA120B 🚗	MA		25	TO-247
MSC025SMA120B4	MA			TO-247-4
MSC025SMA120B4N 🚗	MA			TO-247-4 Notch
MSC025SMA120J	MA			SOT-227
MSC025SMA120S	MA			TO-268
MSC025SMA120SD	MA			TO-263-7-XL
MSC025SMB120B	MB			TO-247
MSC025SMB120B4N 🚗	MB			TO-247-4 Notch
MSC025SMB120Q 🚗	MB			QDPAK
MSC025SMB120SD 🚗	MB			TO-263-7 XL
MSC020SMB120B 🚗	MB		20	TO-247
MSC020SMB120B4N 🚗	MB			TO-247-4 Notch
MSC020SMB120Q 🚗	MB			QDPAK
MSC020SMB120SD 🚗	MB			TO-263-7 XL
MSC017SMA120B 🚗	MA		17	TO-247
MSC017SMA120B4	MA			TO-247-4
MSC017SMA120B4N 🚗	MA			TO-247-4 Notch
MSC017SMA120J	MA			SOT-227
MSC017SMA120S	MA			TO-268
MSC017SMA120SD	MA			TO-263-7-XL
MSC750SMA140SD 🚗	MA	1400	750	TO-263-7-XL
MSC750SMA170B	MA	1700	750	TO-247
MSC750SMA170B4	MA			TO-247-4
MSC750SMA170B4N	MA			TO-247-4 Notch
MSC750SMA170S	MA			TO-268
MSC750SMA170SA	MA			TO-263-7
MSC750SMA170SD	MA			TO-263-7 XL
MSC035SMA170B	MA		35	TO-247
MSC035SMA170B4	MA			TO-247-4
MSC035SMA170B4N	MA			TO-247-4 Notch
MSC035SMA170S	MA			TO-268
MSC400SMA330B4N	MA	3300	400	TO-247-4 Notch
MSC080SMA330B4N	MA		80	TO-247-4 Notch
MSC025SMA330B4N	MA		25	TO-247-4 Notch

🚗 Auto-Qualified Part



Power MOS 8™ MOSFETs/FREDFETs

Power MOS 8 is Microchip's latest family of high-speed, high-voltage (500-1200V) N-channel switch-mode power transistors with lower EMI characteristics and lower cost compared to previous generation devices. These new MOSFETs/FREDFETs have been optimized for both hard and soft switching in high-frequency, high-voltage applications rated above 500W. There are 2 product types in the Power MOS 8 MOSFET family:

1) MOSFET

2) FREDFETs have a fast recovery body diode characteristic, providing high commutation dv/dt ruggedness and high reliability in ZVS circuits.

Features

- Fast switching
- Low EMI
- Quiet switching
- Avalanche-energy rated
- Low gate charge

Applications

- Power factor correction
- Server and telecom power systems
- Solar inverters
- Semiconductor capital equipment
- Induction heating
- Arc welding
- Plasma cutting
- Battery chargers
- Medical

The new Power MOS 8 series is a result of extensive research into quiet switching. Input and reverse transfer capacitance values as well as their ratio were set at specific values to achieve quiet switching with minimal switching loss. The Power MOS 8 series of devices are inherently quiet switching, stable when connected in parallel and very efficient.

Body Diode Options

As with previous generation products, Power MOS 8 MOSFETs and FREDFETs are available in all voltage ratings. A FREDFET is a MOSFET with a faster recovery intrinsic body diode. This results in improved reliability in ZVS circuits due to shorter minority carrier lifetime and increased commutation dv/dt ruggedness. If a fast recovery body diode is not needed, MOSFET versions are available.

Power MOS 8™ MOSFETs/FREDFETs

$V_{BR(DSS)}$ (V)	$R_{DS(on)}$ (Ω) Max	I_D (A)	MOSFET Part Number	I_D (A)	FREDFET Part Number	Package Style
1200	4.20			4	APT4F120K	TO-220
	4.20			4	APT4F120S	D3PAK
	3.80	5	APT4M120K			TO-220
	2.40			7	APT7F120B	TO-247 or D3PAK
	2.10	8	APT7M120B			TO-247
	1.20			14	APT13F120B	TO-247 or D3PAK
	1.10	14	APT14M120B			TO-247 or D3PAK
	0.70			23	APT22F120B2	T-MAX® or TO-264
	0.63	24	APT24M120B2			T-MAX or TO-264
	0.58			27	APT26F120B2	T-MAX or TO-264
	0.58			18	APT17F120J	SOT-227
	0.53	29	APT28M120B2			T-MAX or TO-264
	0.53	19	APT19M120J			SOT-227
	0.32			33	APT32F120J	SOT-227
	0.29	35	APT34M120J			SOT-227
1000	2.00			7	APT7F100B	TO-247
	1.80	8	APT8M100B			TO-247
	1.60			9	APT9F100B	TO-247
	1.40	9	APT9M100B			TO-247 or D3PAK
	0.98			14	APT14F100B	TO-247 or D3PAK
	0.88	14	APT14M100B			TO-247 or D3PAK
	0.78			17	APT17F100B	TO-247 or D3PAK
	0.70	18	APT18M100B			TO-247 or D3PAK
	0.44			30	APT29F100B2	T-MAX or TO-264
	0.44			20	APT19F100J	SOT-227
	0.38	32	APT31M100B2	35		T-MAX or TO-264
	0.38	21	APT21M100J	23		SOT-227
	0.38			35	APT34F100B2	T-MAX or TO-264
	0.38			23	APT22F100J	SOT-227
	0.33	37	APT37M100B2			T-MAX or TO-264
	0.33	25	APT25M100J			SOT-227
	0.20			42	APT41F100J	SOT-227
	0.18	45	APT45M100J			SOT-227
800	0.90			12	APT11F80B	TO-247
	0.80	13	APT12M80B			TO-247
	0.58			18	APT17F80B	TO-247 or D3PAK
	0.53	19	APT18M80B			TO-247
	0.43			23	APT22F80B	TO-247 or D3PAK
	0.39	25	APT24M80B			TO-247 or D3PAK
	0.24			41	APT38F80B2	T-MAX or TO-264
	0.21	43	APT41M80B2			T-MAX or TO-264
	0.21			47	APT44F80B2	T-MAX or TO-264
	0.21			31	APT29F80J	SOT-227
	0.19	49	APT48M80B2			T-MAX or TO-264
	0.19	33	APT32M80J			SOT-227
	0.11			57	APT53F80J	SOT-227
	0.10	60	APT58M80J			SOT-227

Part numbers for D3PAK packages—replace "B" with "S" in part number.
Part numbers for TO-264 packages—replace "B2" with "L" in part number.



TO-247 [B]



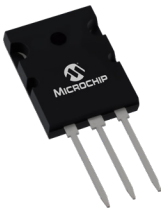
T-MAX® [B2]



SOT-227 [J] (Isolated Base)



TO-220 [K]



TO-264 [L]



TO-268 (D3PAK) [S]

Power MOS 8 MOSFETs/FREDFETs (Continued)

$V_{BR(DSS)}$ (V)	$R_{DS(on)}$ (Ω) Max	I_D (A)	MOSFET Part Number	I_D (A)	FREDFET Part Number	Package Style
600	0.37			19	APT18F60B	TO-247
	0.29			24	APT23F60B	TO-247
	0.19	36	APT34M60B	36	APT34F60B	TO-247 or D3PAK
	0.15	45	APT43M60B2	45	APT43F60B2	T-MAX® or TO-264
	0.11	60	APT56M60B2	60	APT56F60B2	T-MAX or TO-264
	0.11	42	APT39M60J	42	APT39F60J	SOT-227
	0.09	70	APT66M60B2	70	APT66F60B2	T-MAX or TO-264
	0.09	49	APT47M60J	49	APT47F60J	SOT-227
	0.055	84	APT80M60J	84	APT80F60J	SOT-227
500	0.24			24	APT24F50B	TO-247
	0.19			30	APT30F50B	TO-247 or D3PAK
	0.15			37	APT37F50B	TO-247 or D3PAK
	0.13			43	APT42F50B	TO-247 or D3PAK
	0.10	56	APT56M50B2	56	APT56F50B2	T-MAX or TO-264
	0.10	38	APT38M50J	38	APT38F50J	SOT-227
	0.075	75	APT75M50B2	75	APT75F50B2	T-MAX or TO-264
	0.075	51	APT51M50J	51	APT51F50J	SOT-227
	0.065	84	APT84M50B2	84	APT84F50B2	T-MAX or TO-264
	0.065	58	APT58M50J	58	APT58F50J	SOT-227
	0.036	103	APT100M50J	103	APT100F50J	SOT-227

Part numbers for D3PAK packages—replace "B" with "S" in part number.
Part numbers for TO-264 packages—replace "B2" with "L" in part number.



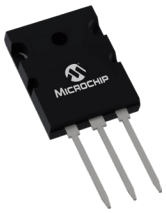
TO-247 [B]



T-MAX® [B2]



SOT-227 [J]
(Isolated Base)



TO-264 [L]



TO-268 (D3PAK) [S]

Low-Voltage Power MOS V® MOSFETs/FREDFETs

$V_{BR(DSS)}$ (V)	$R_{DS(on)}$ (Ω) Max	I_D (A)	MOSFET Part Number	I_D (A)	FREDFET Part Number	Package Style
300	0.085	40	APT30M85BVRG			TO-247
	0.070	48	APT30M70BVRG	48	APT30M70BVFRG	TO-247
	0.040	70	APT30M40JVR	70	APT30M40JVFR	SOT-227
	0.019	130	APT30M19JVR	130	APT30M19JVFR	SOT-227
200	0.045	56	APT20M45BVRG	56	APT20M45BVFRG	TO-247 or D3PAK
	0.038	67	APT20M38BVRG			TO-247 or D3PAK
	0.022	97	APT20M22JVR	100	APT20M22LVFRG	TO-264
	0.022	100	APT20M22LVRG			SOT-227
	0.018	100	APT20M18B2VRG	100	APT20M18B2VFRG	T-MAX® or TO-264
	0.011	175	APT20M11JVR	175	APT20M11JVFR	SOT-227

Part numbers for D3PAK packages—replace "B" with "S" in part number.
Part numbers for TO-264 packages—replace "B2" with "L" in part number.

Ultra-Fast, Low Gate Charge MOSFETs



For 250 kHz–2 MHz Switching Applications

The ultra-fast, low gate charge MOSFET family combines the lowest gate charge available in the industry with Microchip's proprietary self-aligned aluminum metal gate structure. The result is a MOSFET capable of extremely fast switching speeds and very low switching losses. The metal gate structure and the layout of these chips provide an internal Series Gate Resistance (EGR) an order of magnitude lower than competitive devices built with a polysilicon gate.

These devices are ideally suited for high-frequency and pulsed high-voltage applications.

Typical Applications

- Class D amplifiers up to 2 MHz
- High-voltage pulsed DC
- AM transmitters
- Plasma deposition/etch

Features

- Series gate resistance (R_G) <0.1Ω
- T_R and T_F times of <10 ns
- Industry's lowest gate charge

Benefits

- Fast switching, uniform signal propagation
- Pulse power applications
- Fast switching, reduced gate drive power

Ultra-Fast, Low Gate Charge MOSFETs

$V_{BR(DSS)}$ (V)	$R_{DS(on)}$ (mOhm) Max	I_D (A)	MOSFET Part Number	FREDFET Part Number	Package Style
1200	4700	3.5		APT1204R7BFLLG	TO-247 or D3PAK
	1400	9		APT1201R4BFLLG	TO-247
	570	22	APT12057B2LLG		T-MAX®
1000	900	12	APT10090BLLG		TO-247
	780	14	APT10078BLLG		TO-247 or D3PAK
	450	23	APT10045B2LLG		T-MAX or TO-264
	450	21	APT10045JLL		SOT-227
	370	25		APT10035JFLL	SOT-227
	370	28		APT10035B2FLLG	T-MAX
	350	28	APT10035LLLG		TO-264
	350	25	APT10035JLL		SOT-227
	260	38		APT10026L2FLLG	264-MAX™
	260	30	APT10026JLL	APT10026JFLL	SOT-227
	210	37	APT10021JLL	APT10021JFLL	SOT-227
800	260	29		APT8024JFLL	SOT-227
	240	29	APT8024JLL		SOT-227
	200	38	APT8020B2LLG	APT8020B2FLLG	T-MAX or TO-264
	200	33	APT8020JLL		SOT-227
	160	42		APT8014JFLL	SOT-227
	140	52	APT8014L2LLG	APT8014L2FLLG	264-MAX
	140	42	APT8014JLL		SOT-227
	110	51	APT8011JLL	APT8011JFLL	T-MAX or TO-264
500	140	35	APT5014BLLG		TO-247
	100	46	APT5010B2LLG	APT5010B2FLLG	T-MAX or TO-264
	75	51	APT50M75JLL	APT50M75JFLL	SOT-227
	75	57	APT50M75B2LLG		T-MAX or TO-264
	65	67	APT50M65LLLG	APT50M65B2FLLG	TO-264
	65	58	APT50M65JLL	APT50M65JFLL	SOT-227
	50	71	APT50M50JLL	APT50M50JFLL	SOT-227
	38	88	APT50M38JLL	APT50M38JFLL	SOT-227

Part numbers for D3PAK packages—replace "B" with "S" in part number.
Part numbers for TO-264 packages—replace "B2" with "L" in part number.



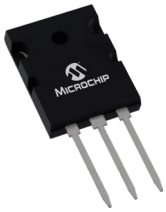
TO-247 [B]



T-MAX® [B2]



SOT-227 [J]
(Isolated Base)



TO-264 [L]



264-MAX™ [L2]



TO-268 (D3PAK) [S]



Superjunction MOSFETs

$V_{BR(DSS)}$ (V)	$R_{DS(on)}$ (mOhm) Max	$I_{D(CONT)}$ (A)	Part Number	Package Style
600	**Server Series**			
	45	60	APT60N60BCSG	TO-247 or D3PAK
	C7 Technology			
	18	100	APT100N60BC7	TO-247
	55	40	APT40N60BC7	TO-247
	C6 Technology			
	125	30	APT30N60BC6	TO-247
	99	38	APT38N60BC6	TO-247
	70	53	APT53N60BC6	TO-247 or D3PAK
	41	77	APT77N60BC6	TO-247 or D3PAK
	35	106	APT106N60B2C6	T-MAX or TO-264

Part numbers for D3PAK packages—replace "B" with "S" in part number.
Part numbers for TO-264 packages—replace "B2" with "L" in part number.



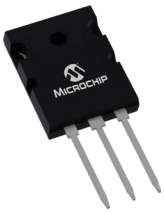
TO-247 [B]



T-MAX® [B2]



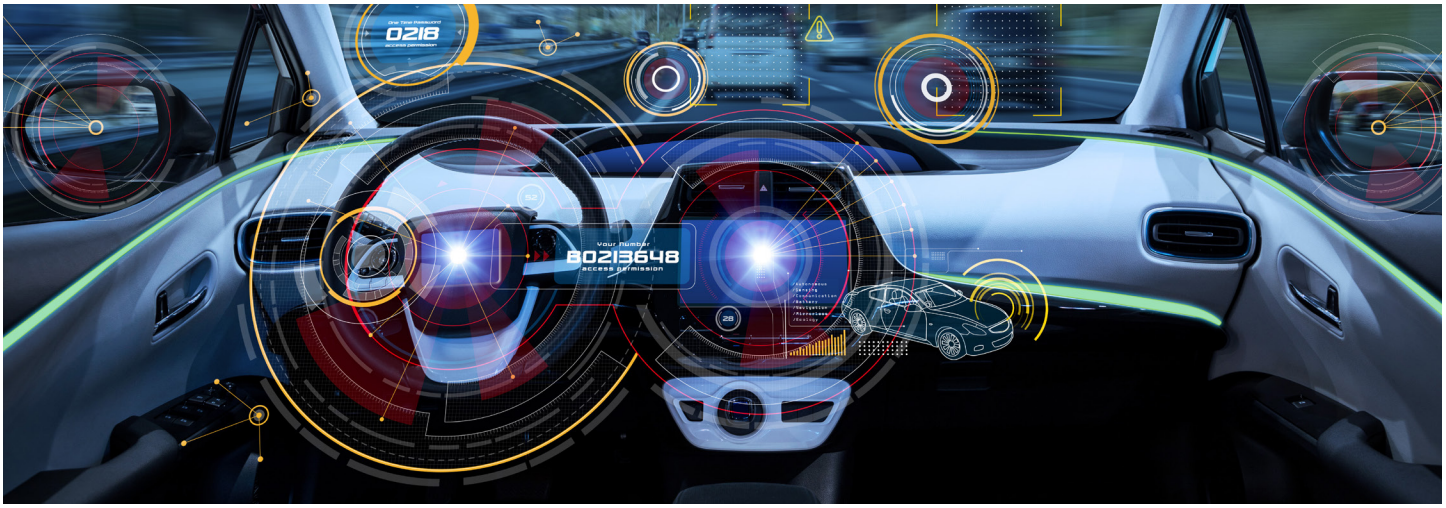
SOT-227 [J]
(Isolated Base)



TO-264 [L]



TO-268 (D3PAK) [S]



Linear MOSFETs

What is a Linear MOSFET?

A MOSFET specifically designed to be more robust than a standard MOSFET when operated with both high voltage and high current near DC conditions (>100 ms).

The Problem with SMPS MOSFETs

MOSFETs optimized for high-frequency SMPS applications have poor high voltage DC SOA. Most SMPS-type MOSFETs overstate SOA capability at high voltage on the datasheets. Above ~30V and DC conditions, SOA drops faster than is indicated by Power Dissipation (PD) limited operation. For pulsed loads (t <10 ms), there is generally no problem using a standard MOSFET.

Technology Innovation

Introduced in 1999, Microchip modified its proprietary patented self-aligned metal gate MOSFET technology for enhanced performance in high voltage, linear applications. These linear MOSFETs typically provide 1.5–2.0 times the DC SOA capability at high voltage compared to other MOSFET technologies optimized for switching applications.

A Design Will Need Linear MOSFETs in the Following Situations

- High current and greater than 200 volts at greater than 100 milliseconds
- Used as a variable power resistor
- Soft start application (limit surge currents)
- Linear amplifier circuit

Typical Applications

- Active loads above 200 volts, such as DC dynamic loads for testing power supplies, batteries, fuel cells, etc.
- High voltage, high current, constant current sources

$V_{BR(DSS)}$ (V)	$R_{DS(on)}$ (Ω) Max	$I_{D(CONT)}$ (A)	SOA (W)	Part Number
1000	60	18	325	APL1001J
600	125	49	425	APL602B2G
	125	43	325	APL602J
500	12	43	325	APL501J
	90	58	425	APL502B2G
	90	52	300	APL502J
Part numbers for TO-264 packages—replace "B2" with "L" in part number.				



T-MAX® [B2]



SOT-227 [J]
(Isolated Base)



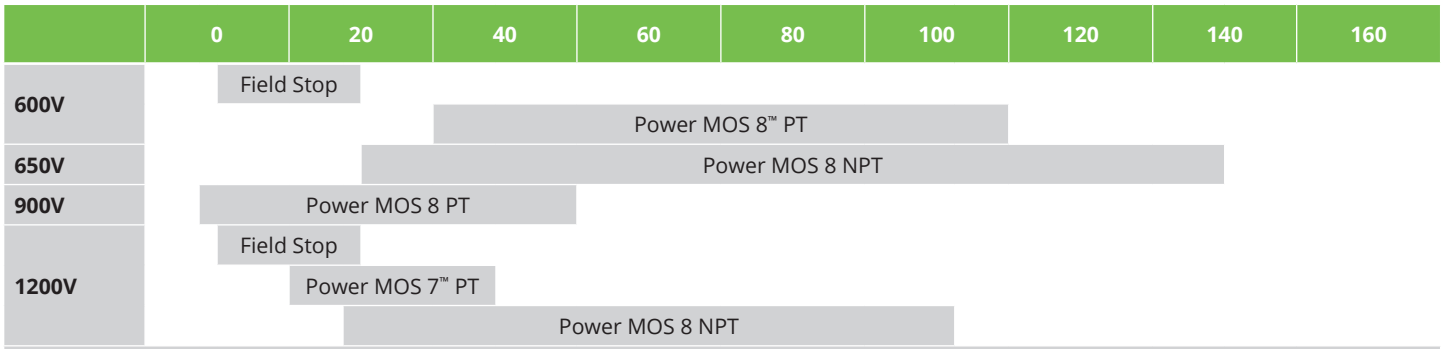
TO-264 [L]



IGBTs

IGBT products from Microchip provide high-quality solutions for a wide range of high-voltage and high-power applications. The switching frequency range spans from DC for minimal conduction loss to 150 kHz for very-high-power-density Switch Mode Power Supply (SMPS) applications. The frequency range for each product type is shown in the following graph. Each IGBT product represents the latest in IGBT technology, providing the best possible performance/cost combination for the targeted application. There are six product series that utilize three different IGBT technologies: Non-Punch-Through (NPT), Punch-Through (PT) and field stop.

IGBT Switching Frequency Ranges (kHz, Hard Switched)



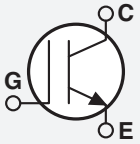
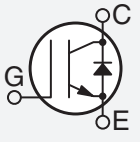
Note: Frequency ranges shown are typical for a 50 A IGBT. Refer to product datasheet maximum frequency versus current graph for more information.

Standard Series	Voltage Ratings (V)	Technology	Easy to Parallel	Short Circuit Safe Operating Area (SOA)	Parameter
MOS 7	600, 900, 1200	PT			Ultra-low gate charge
MOS 8	600, 650, 900, 1200	PT, NPT			Highest efficiency
Field Stop Trench Gate	600, 1200	Field Stop	•	•	Lowest conduction loss

Product Options

All standard IGBT products are available as a single IGBT or as a co-packaged product with an anti-parallel DQ series diode. Package options include TO-220, TO-247, T-MAX®, TO-264 and SOT-227. Customized products are available; contact the factory for details.

IGBTs—Punch-Through

	$V_{(BR)CES}$ (V)	$V_{CE(ON)}$ (V) Typ 25°C	I_{C2} (A) 110°C	Maximum I_C (A) at Frequency		Part Number	Package Style
POWER MOS 7™	**Single**			**100 kHz**	**200 kHz**		
	600	2.2	27	20	12	APT15GP60BG	TO-247
		2.2	49	37	24	APT30GP60BG	TO-247
		2.2	62	42	26	APT40GP60BG	TO-247
		2.2	40	25	16	APT40GP60J	SOT-227
		2.2	72	44	26	APT50GP60BG	TO-247
		2.2	46	28	19	APT50GP60J	SOT-227
		2.2	100	72	45	APT80GP60B2G	T-MAX®
				50 kHz	**100 kHz**		
		2.2	96	76	54	APT65GP60B2G	T-MAX
		2.2	60	49	34	APT65GP60J	SOT-227
		2.2	68	59	39	APT80GP60J	SOT-227
	900	3.2	36	31	21	APT25GP90BG	TO-247
		3.2	50	36	22	APT40GP90BG	TO-247
		3.2	32	20	14	APT40GP90J	SOT-227
	1200			**50 kHz**	**100 kHz**		
• Ultra-low gate charge • Co-packaged with high-speed DQ diode		3.3	33	19	11	APT25GP120BG	TO-247
		3.3	46	24	15	APT35GP120BG	TO-247
		3.3	54	29	18	APT45GP120BG	TO-247
		3.3	91	40	21	APT75GP120B2G	T-MAX
				20 kHz	**40 kHz**		
		3.3	34	31	20	APT45GP120J	SOT-227
		3.3	57	43	23	APT75GP120J	SOT-227
	Co-packaged (IGBT & "DQ" FRED)			**50 kHz**	**100 kHz**		
	600	2.2	60	51	33	APT65GP60JDQ2	SOT-227
		2.2	96	79	54	APT65GP60L2DQ2G	264-MAX®
		2.2	68	59	39	APT80GP60JDQ3	SOT-227
				100 kHz	**200 kHz**		
		2.2	27	19	12	APT15GP60BDQ1G	TO-247
		2.2	49	35	22	APT30GP60BDQ1G	TO-247
		2.2	62	41	26	APT40GP60B2DQ2G	TO-247
		2.2	40	25	16	APT40GP60JDQ2	SOT-227
		2.2	72	44	26	APT50GP60B2DQ2G	TO-247
		2.2	46	27	17	APT50GP60JDQ2	SOT-227
	900			**20 kHz**	**40 kHz**		
		3.2	21	27	20	APT15GP90BDQ1G	TO-247
		3.2	36	53	34	APT25GP90BDQ1G	TO-247
		3.2	50	56	40	APT40GP90B2DQ2G	T-MAX
		3.2	27	33	24	APT40GP90JDQ2	SOT-227



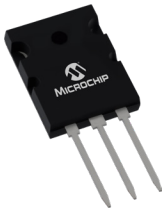
TO-247 [B]



T-MAX® [B2]



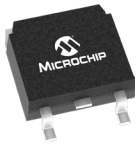
SOT-227 [J]



TO-264 [L]

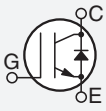


264-MAX™ [L2]



TO-268 (D3PAK) [S]

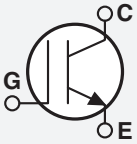
	$V_{(BR)CES}$ (V)	$V_{CE(ON)}$ (V) Typ 25°C	I_{C2} (A) 110°C	Maximum I_C (A) at Frequency		Part Number	Package Style
				50 kHz	**100 kHz**		
	1200	3.3	20	17	11	APT13GP120BDQ1G	TO-247
		3.3	33	19	12	APT25GP120BDQ1G	TO-247
		3.3	46	25	15	APT35GP120B2DQ2G	T-MAX
		3.3	54	29	18	APT45GP120B2DQ2G	T-MAX
				20 kHz	**40 kHz**		
		3.3	34	30	16	APT45GP120JDQ2	SOT-227
		3.3	46	44	23	APT75GP120JDQ3	SOT-227
POWER MOS 7	**Co-packaged (IGBT & SiC SBD)**			**50 kHz**	**80 kHz**		
	1200	3.3	33	30	22	APT25GP120BSC15	TO-247
		3.3	46	33	27	APT35GP120B2SC20	T-MAX
		3.3	57	35	23	APT75GP120JSC30	SOT-227

	$V_{(BR)CES}$ (V)	$V_{CE(ON)}$ (V) Typ 25°C	I_{C2} (A) 110°C	Maximum I_C (A) at Frequency		Part Number	Package Style
POWER MOS 8™	**Single**			**50 kHz**	**80 kHz**		
	600	2	54	30	23	APT54GA60B	TO-247
		2	68	35	27	APT68GA60B	TO-247
		2	80	40	31	APT80GA60B	TO-247
		2	102	51	39	APT102GA60B2	T-MAX or TO-264
	900			**25 kHz**	**50 kHz**		
		2.5	35	17	10	APT35GA90B	TO-247
		2.5	43	21	13	APT43GA90B	TO-247
		2.5	64	29	19	APT64GA90B	TO-247
		2.5	80	34	23	APT80GA90B	TO-247
	Co-packaged (IGBT & "DQ" FRED)			**50 kHz**	**80 kHz**		
	600	2	47	N/A	N/A	APT47GA60JD40	SOT-227
		2	54	30	23	APT54GA60BD30	TO-247
		2	60	48	36	APT60GA60JD60	SOT-227
		2	68	35	27	APT68GA60B2D40	T-MAX or TO-264
		2	80	40	31	APT80GA60LD40	TO-264
	900			**25 kHz**	**50 kHz**		
		2.5	27	14	8	APT27GA90BD15	TO-247
		2.5	35	17	10	APT35GA90BD15	TO-247
		2.5	43	21	13	APT43GA90BD30	TO-247
		2.5	46	33	21	APT46GA90JD40	SOT-227
		2.5	64	29	19	APT64GA90B2D30	T-MAX or TO-264
		2.5	80	34	23	APT80GA90LD40	TO-264
	Co-packaged (IGBT & SiC SBD)			**50 kHz**	**80 kHz**		
	900	2.5	43	24	18	APT43GA90BSC30	TO-247
		2.5	46	35	21	APT46GA90JSC30	SOT-227
		2.5	64	31	22	APT64GA90B2SC30	T-MAX
		2.5	80	43	31	APT80GA90B2SC50	T-MAX

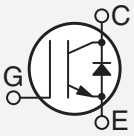
Part numbers for D3PAK packages—replace "B" with "S" in part number.
Part numbers for TO-264 packages—replace "B2" with "L" in part number.

IGBTs—Non-Punch-Through

	$V_{(BR)CES}$ (V)	$V_{CE(ON)}$ (V) Typ 25°C	I_{C2} (A) 110°C	Maximum I_C (A) at Frequency		Part Number	Package Style
POWER MOS 8™	**Single**			**100 kHz**	**150 kHz**		
	600	1.9	70	52	39	APT70GR65B	TO-247
				50 kHz	**100 kHz**		
		1.9	95	75	42	APT95GR65B2	T-MAX®
	1200			**100 kHz**	**150 kHz**		
		2.5	25[1]	25	21	APT25GR120B	TO-247
				50 kHz	**80 kHz**		
		2.5	50	48	36	APT50GR120B2	T-MAX
		2.5	50	48	36	APT50GR120L	TO-264
				25 kHz	**50 kHz**		
		2.5	70	75	53	APT70GR120B2	T-MAX
		2.5	70	75	53	APT70GR120L	TO-264
		2.5	70[2]	50	30	APT70GR120J	SOT-227
		2.5	85[3]	80	46	APT85GR120B2	T-MAX
		2.5	85[3]	80	46	APT85GR120L	TO-264
		2.5	85[4]	75	50	APT85GR120J	SOT-227
	Co-packaged (IGBT & "DQ" FRED)			**50 kHz**	**100 kHz**		
	1200	2.5	25[1]	39	25	APT25GR120BD15	TO-247
				25 kHz	**50 kHz**		
		2.5	50[5]	45	32	APT50GR120JD30	SOT-227
		2.5	70[2]	50	30	APT70GR120JD60	SOT-227
		2.5	85[4]	75	50	APT85GR120JD60	SOT-227



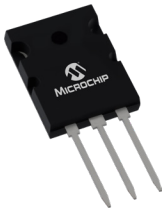
- High-speed switching
- Low switching losses
- Easy to parallel




TO-247 [B]


T-MAX® [B2]


SOT-227 [J]


TO-264 [L]


TO-268 (D3PAK) [S]

Continuous Drain Current test conditions:

1 T_C = 125°C

2 T_C = 86°C

3 T_C = 100°C

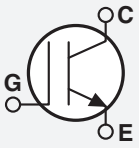
4 T_C = 75°C

5 T_C = 90°C

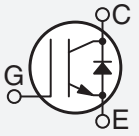
Current at frequency test conditions: T_J = 125°C, T_C = 100°C except SOT-227 where T_C = 80°C, V_{CC} = 67% rated voltage hard switch.

IGBTs—Field Stop

	$V_{(BR)CES}$ (V)	$V_{CE(ON)}$ (V) Typ 25°C	I_{C2} (A) 110°C	Maximum I_C (A) at Frequency		Part Number	Package Style
Field Stop	**Single**			**15 kHz**	**30 kHz**		
	600	1.5	24	24	17	APT20GN60BG	TO-247
		1.5	37	34	26	APT30GN60BG	TO-247
		1.5	64	57	40	APT50GN60BG	TO-247
		1.5	93	78	55	APT75GN60BG	TO-247
		1.5	123	90	58	APT150GN60J	SOT-227
		1.5	135	103	71	APT100GN60B2G	T-MAX®
		1.5	190	90	57	APT150GN60B2G	T-MAX
		1.5	230	120	80	APT200GN60B2G	T-MAX
		1.5	158	110	79	APT200GN60J	SOT-227
	1200			**10 kHz**	**20 kHz**		
		1.7	33	42	26	APT25GN120BG	TO-247 or D3PAK
		1.7	46	45	32	APT35GN120BG	TO-247 or D3PAK
		1.7	66	56	40	APT50GN120B2G	T-MAX
		1.7	70	46	27	APT100GN120J	SOT-227
		1.7	73			APT50GH120B	TO-247
		1.7	102			APT100GH120J	SOT-227
		1.7	99	78	51	APT75GN120B2G	T-MAX or TO-264
		1.7	120	95	57	APT100GN120B2G	T-MAX
		1.7	99	65	40	APT150GN120J	SOT-227
	Co-packaged (IGBT & "DQ" FRED)			**15 kHz**	**30 kHz**		
	600	1.5	24	24	17	APT20GN60BDQ1G	TO-247
		1.5	37	35	26	APT30GN60BDQ2G	TO-247
		1.5	64	57	40	APT50GN60BDQ2G	TO-247
		1.5	93	87	55	APT75GN60LDQ3G	TO-264
		1.5	123	90	58	APT150GN60JDQ4	SOT-227
		1.5	135	102	70	APT100GN60LDQ4G	TO-264
		1.5	190	108	57	APT150GN60LDQ4G	TO-264
		1.5	158	110	79	APT200GN60JDQ4	SOT-227
	1200			**10 kHz**	**20 kHz**		
		1.7	22	24	17	APT15GN120BDQ1G	TO-247 or D3PAK
		1.7	33	43	26	APT25GN120B2DQ2G	T-MAX
		1.7	46	45	31	APT35GN120L2DQ2G	264-MAX™
		1.7	72			APT75GH120JD30	SOT-227
		1.7	73			APT50GH120BD30	TO-247
		1.7	102			APT100GH120JD60	SOT-227
		1.7	114			APT75GH120BD40	TO-247
		1.7	57	43	26	APT75GN120JDQ3	SOT-227
		1.7	70	44	27	APT100GN120JDQ4	SOT-227
		1.7	99	108	75	APT150GN120JDQ4	SOT-227



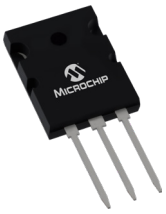
- Trench technology
- Short circuit rated
- Lowest conduction loss
- Easy paralleling
- Co-packaged with high-speed DQ diode




TO-247[B]


T-MAX®[B2]


SOT-227[J]


TO-264[L]


264-MAX™[L2]


TO-268 (D3PAK) [S]

IGBTs—Field Stop (Continued)

	$V_{(BR)CES}$ (V)	$V_{CE(ON)}$ (V) Typ 25°C	I_{C2} (A) 110°C	Maximum I_C (A) at Frequency		Part Number	Package Style
• Trench technology • Short circuit rated • Lowest conduction loss • Easy paralleling	**Co-packaged (IGBT & SiC SBD)**						
	1200	1.7	72			APT75GH120JSC30	SOT-227
		1.7	73			APT50GH120BSC20	TO-247
		1.7	102			APT100GH120JSC50	SOT-227
Part numbers for D3PAK packages—replace "B" with "S" in part number. Part numbers for TO-264 packages—replace "B2" with "L" in part number.							

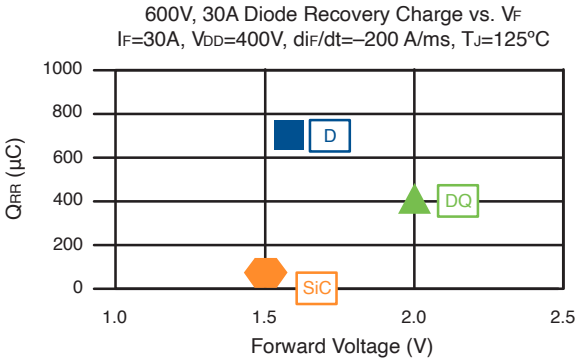
Current at frequency test conditions: T_J = 125°C, T_C = 100°C except SOT-227 where T_C = 80°C, V_{CC} = 67% rated voltage hard switch.



Schottky Barrier Diodes, Fast and Ultra-Fast Recovery Diodes

Microchip offers four series of discrete diode products: the medium-speed medium V_F D series, the high-speed DQ series, the silicon Schottky S series and the SiC Schottky Barrier Diode series. These series of diodes are designed to provide high-quality solutions to a wide range of high-voltage, high-power application requirements, ranging from fast recovery for continuous conduction mode power factor correction to low conduction loss for output rectification. The following table summarizes each product family's distinguishing features and potential applications.

The following graph shows the relative recovery speed and forward voltage positions of D, DQ, and SiC series diodes.



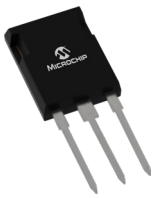
Fast, Ultra-Fast and Schottky Diodes

Series	Voltage Ratings	Features	Applications	Comment
D	200, 300, 400, 600, 1000, 1200	Medium V_F Medium speed	Freewheeling diode Output rectifier DC–DC converter	Proprietary platinum process
DQ	600, 1000, 1200	High speed Avalanche rated	PFC Freewheeling diode DC–DC converter	Stepped EPI improves softness Proprietary platinum process
Schottky	200	Low V_F Avalanche rated	Output rectifier Freewheeling diode DC–DC converter	
SiC Schottky	700, 1200, 1700, 3300	Zero reverse recovery	PFC Freewheeling diode DC–DC converter	Low switching losses, high power density and high-temperature operation

mSiC Diodes

Part Number	Voltage (V)	I_F (A)	Package Style
MSC010SDA070B	700	10	TO-247-2
MSC010SDA070K		10	TO-220
MSC010SDA070S		10	TO-268
MSC030SDA070B		30	TO-247-2
MSC030SDA070K		30	TO-220
MSC030SDA070S		30	TO-268
MSC050SDA070B		50	TO-247-2
MSC050SDA070S		50	TO-268
MSC010SDA120B	1200	10	TO-247-2
MSC010SDA120K		10	TO-220
MSC015SDA120B		15	TO-247-2
MSC015SDA120K		15	TO-220
MSC020SDA120B		20	TO-247-2
MSC020SDA120K		20	TO-220
MSC020SDA120S		20	TO-268
MSC030SDA120B		30	TO-247-2
MSC030SDA120K		30	TO-220
MSC030SDA120S		30	TO-268
MSC050SDA120B		50	TO-247-2
MSC050SDA120S		50	TO-268
MSC010SDA170B	1700	10	TO-247-2
MSC030SDA170B		30	TO-247-2
MSC050SDA170B		50	TO-247-2
MSC030SDA330B	3300	30	TO-247-2
MSC090SDA330B2		90	T-MAX®
MSC030SDA070BCT	700 Dual Diode (Common Cathode)	2 × 30	TO-247
MSC050SDA070BCT		2 × 50	TO-247
MSC030SDA120BCT	1200 Dual Diode (Common Cathode)	2 × 30	TO-247
MSC050SDA120BCT		2 × 50	TO-247
MSC2X30/31SDA070J	700 Dual Diode (Anti-parallel/parallel)	2 × 30	SOT-227
MSC2X50/51SDA070J		2 × 50	SOT-227
MSC2X100/101SDA070J		2 × 100	SOT-227
MSC2X30/31SDA120J	1200 Dual Diode (Anti-parallel/parallel)	2 × 30	SOT-227
MSC2X50/51SDA120J		2 × 50	SOT-227
MSC2X100/101SDA120J		2 × 100	SOT-227
MSC2X30SDA170J	1700 Dual Diode (Anti-parallel/parallel)	2 × 30	SOT-227
MSC2X31SDA170J			SOT-227
MSC2X50SDA170J		2 × 50	SOT-227
MSC2X51SDA170J			SOT-227

Auto-Qualified Part



TO-247-2 [B]



TO-247 [BCT]
Common cathode



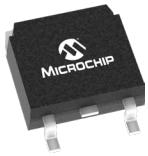
T-MAX® [B2]



SOT-227 [J]
Antiparallel
Configuration
(Isolated Base)



TO-220 [K]



TO-268 (D3PAK) [S]

Si Schottky Barrier Diodes, Fast and Ultra-Fast Recovery Diodes

Volts	I (A)	Forward Voltage Typ 25°C	t(ns) Typ 25°C	Qrr (nC) Typ 125°C at $I_F = I_F$ (avg)	Diode Series	Part Number	Package Style
Single							
1200	15	2.8	21	960	DQ	APT15DQ120BG	TO-247
	15	2.8	21	960	DQ	APT15DQ120KG	TO-220
	15	2.0	32	1300	D	APT15D120BG	TO-247
	15	2.0	32	1300	D	APT15D120KG	TO-220
	30	2.8	24	1800	DQ	APT30DQ120BG	TO-247
	30	2.8	24	1800	DQ	APT30DQ120KG	TO-220
	30	2.0	31	3450	D	APT30D120BG	TO-247 or D3PAK
	40	2.8	26	2200	DQ	APT40DQ120BG	TO-247
	40	2.8	26	2200	DQ	APT40DQ120SG	D3PAK
	60	2.8	30	2800	DQ	APT60DQ120BG	TO-247
	60	2.8	30	2800	DQ	APT60DQ120SG	D3PAK
	60	2.0	38	4000	D	APT60D120BG	TO-247 or D3PAK
	75	2.8	32	3340	DQ	APT75DQ120BG	TO-247
	75	2.8	32	3340	DQ	APT75DQ120SG	D3PAK
1000	15	2.5	20	810	DQ	APT15DQ100BG	TO-247
	15	2.5	20	810	DQ	APT15DQ100KG	TO-220
	15	1.9	28	1550	D	APT15D100BG	TO-247
	15	1.9	28	1550	D	APT15D100KG	TO-220
	30	2.5	22	1250	DQ	APT30DQ100BG	TO-247
	30	2.5	22	1250	DQ	APT30DQ100KG	TO-247
	30	1.9	29	2350	D	APT30D100BG	TO-247
	40	2.5	24	1430	DQ	APT40DQ100BG	TO-247
	60	2.5	29	2325	DQ	APT60DQ100BG	TO-247
	60	1.9	34	3600	D	APT60D100BG	TO-247 or D3PAK
	75	2.5	33	2660	DQ	APT75DQ100BG	TO-247
600	15	2.0	16	250	DQ	APT15DQ60BG	TO-247
	15	2.0	16	250	DQ	APT15DQ60SG	D3PAK
	15	2.0	16	250	DQ	APT15DQ60KG	TO-220
	15	1.6	21	520	D	APT15D60BG	TO-247
	15	1.6	21	520	D	APT15D60KG	TO-220
	30	2.0	19	400	DQ	APT30DQ60BG	TO-247
	30	2.0	19	400	DQ	APT30DQ60KG	TO-220
	30	1.6	23	700	D	APT30D60BG	TO-247 or D3PAK
	40	2.0	22	480	DQ	APT40DQ60BG	TO-247
	60	2.0	26	640	DQ	APT60DQ60BG	TO-247
	60	2.0	26	640	DQ	APT60DQ60SG	D3PAK
	60	1.6	40	920	D	APT60D60SG	D3PAK
	75	2.0	29	650	DQ	APT75DQ60BG	TO-247
	75	2.0	29	650	DQ	APT75DQ60SG	D3PAK
400	15	1.3	19	300	D	APT15D40KG	TO-220
	30	1.3	22	360	D	APT30D40BG	TO-247
	60	1.3	30	540	D	APT60D40BG	TO-247
200	30	1.1	21	150	D	APT30D20BG	TO-247
	30	0.83	25	448	Schottky	APT30S20BG	TO-247 or D3PAK
	60	1.1	30	250	D	APT60D20BG	TO-247
	60	0.83	35	490	Schottky	APT60S20BG	TO-247 or D3PAK
	100	0.89	40	690	Schottky	APT100S20BG	TO-247

Part numbers for D3PAK—replace "B" with "S" in part number.



TO-247 [B]



TO-220 [K]



TO-268 (D3PAK) [S]

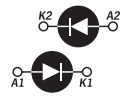
Si Schottky Barrier Diodes, Fast and Ultra-Fast Recovery Diodes

Volts	I (A)	Forward Voltage Typ 25°C	t(ns) Typ 25°C	Qrr (nC) Typ 125°C at $I_F = I_F$ (avg)	Diode Series	Part Number	Package
Dual							
1200	2x27	2	31	3450	D	APT2X30D120J	SOT-227
	2x30	2.6	25	1800	DQ	APT2X30DQ120J	SOT-227
	2x53	2.0	38	4000	D	APT2X60D120J	SOT-227
	2x60	2.5	30	2890	DQ	APT2X60DQ120J	SOT-227
	2x93	2.0	47	5350	D	APT2X100D120J	SOT-227
	2x100	2.4	45	5240	DQ	APT2X100DQ120J	SOT-227
1000	2x28	1.9	29	2350	D	APT2X30D100J	SOT-227
	2x55	1.9	34	3600	D	APT2X60D100J	SOT-227
	2x60	2.2	30	2350	DQ	APT2X60DQ100J	SOT-227
	2x95	1.9	43	4050	D	APT2X100D100J	SOT-227
	2x100	2.1	45	3645	DQ	APT2X100DQ100J	SOT-227
600	2x30	1.8	20	400	DQ	APT2X30DQ60J	SOT-227
	2x30	1.6	23	700	D	APT2X30D60J	SOT-227
	2x60	1.7	27	650	DQ	APT2X60DQ60J	SOT-227
	2x60	1.6	40	920	D	APT2X60D60J	SOT-227
	2x100	1.6	30	980	DQ	APT2X100DQ60J	SOT-227
	2x100	1.6	34	1450	D	APT2X100D60J	SOT-227
400	2x30	1.3	22	360	D	APT2X30D40J	SOT-227
	2x60	1.3	30	540	D	APT2X60D40J	SOT-227
	2x100	1.3	37	1050	D	APT2X100D40J	SOT-227
300	2x30	1.2	20	150	D	APT2X30D30J	SOT-227
	2x60	1.2	29	370	D	APT2X61D30J	SOT-227
	2x100	1.2	36	650	D	APT2X101D30J	SOT-227
200	2x30	1.1	21	150	D	APT2X30D20J	SOT-227
	2x60	1.1	30	250	D	APT2X61D20J	SOT-227
	2x30	0.80	25	448	Schottky	APT2X31S20J	SOT-227
	2x60	0.83	35	490	Schottky	APT2X61S20J	SOT-227
	2x100	1.1	39	840	D	APT2X100D20J	SOT-227
	2x100	0.89	40	690	Schottky	APT2X101S20J	SOT-227
1200	2x30	2.8	26	2100	DQ	APT30DQ120BCTG	TO-247 [BCT]
1000	2x15	2.5	20	810	DQ	APT15DQ100BCTG	TO-247 [BCT]
	2x15	1.9	28	1550	D	APT15D100BCTG	TO-247 [BCT]
	2x15	1.9	28	1550	D	APT15D100BHBG	TO-247 [BHB]
	2x18	1.9	29	2350	D	APT30D100BCAG	TO-247 [BCA]
	2x30	1.9	29	2360	D	APT30D100BCTG	TO-247 [BCT]
	2x30	1.9	30	2350	D	APT30D100BHBG	TO-247 [BHB]
	2x40	2.5	25	1650	DQ	APT40DQ100BCTG	TO-247 [BCT]
	2x60	2.5	29	2325	DQ	APT60DQ100LCTG	TO-264 [LCT]
	2x60	1.9	35	3600	D	APT60D100LCTG	TO-264 [LCT]
600	2x15	1.6	21	520	D	APT15D60BCTG	TO-247 [BCT]
	2x15	2.0	15	250	DQ	APT15DQ60BCTG	TO-247 [BCT]
	2x15	1.6	20	520	D	APT15D60BCAG	TO-247 [BCA]
	2x30	2.0	22	480	DQ	APT30DQ60BHBG	TO-247 [BHB]
	2x30	2.0	19	400	DQ	APT30DQ60BCTG	TO-247 [BCT]
	2x30	1.6	23	700	D	APT30D60BCTG	TO-247 [BCT]
	2x30	1.6	25	700	D	APT30D60BHBG	TO-247 [BHB]
	2x30	1.6	25	700	D	APT30D60BCAG	TO-247 [BCA]
	2x40	2.0	22	480	DQ	APT40DQ60BCTG	TO-247 [BCT]
	2x60	2.0	26	640	DQ	APT60DQ60BCTG	TO-247 [BCT]
	2x60	1.6	30	920	D	APT60D60LCTG	TO-264 [LCT]
400	2x15	1.3	19	300	D	APT15D40BCTG	TO-247 [BCT]
	2x30	1.3	22	360	D	APT30D40BCTG	TO-247 [BCT]
	2x60	1.3	30	540	D	APT60D40LCTG	TO-264 [LCT]
300	2x30	1.2	25	1300	D	APT30D30BCTG	TO-247 [BCT]
200	2x30	1.1	21	150	D	APT30D20BCTG	TO-247 [BCT]
	2x30	1.1	21	150	D	APT30D20BCAG	TO-247 [BCA]
	2x30	0.80	25	448	Schottky	APT30S20BCTG	TO-247 [BCT]
	2x60	0.83	35	490	Schottky	APT60S20B2CTG	T-MAX® [B2CT]
	2x100	0.89	40	690	Schottky	APT100S20LCTG	TO-264 [LCT]

Part numbers for parallel configuration: replace 30, 60, or 100 with 31, 61, or 101, unless Schottky.
Example: 2X30D120J becomes 2X31D120J.



SOT-227 [J]
Antiparallel
Configuration
(Isolated Base)





TO-247 [BCA]
Common anode



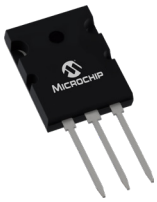
TO-247 [BCT]
Common cathode



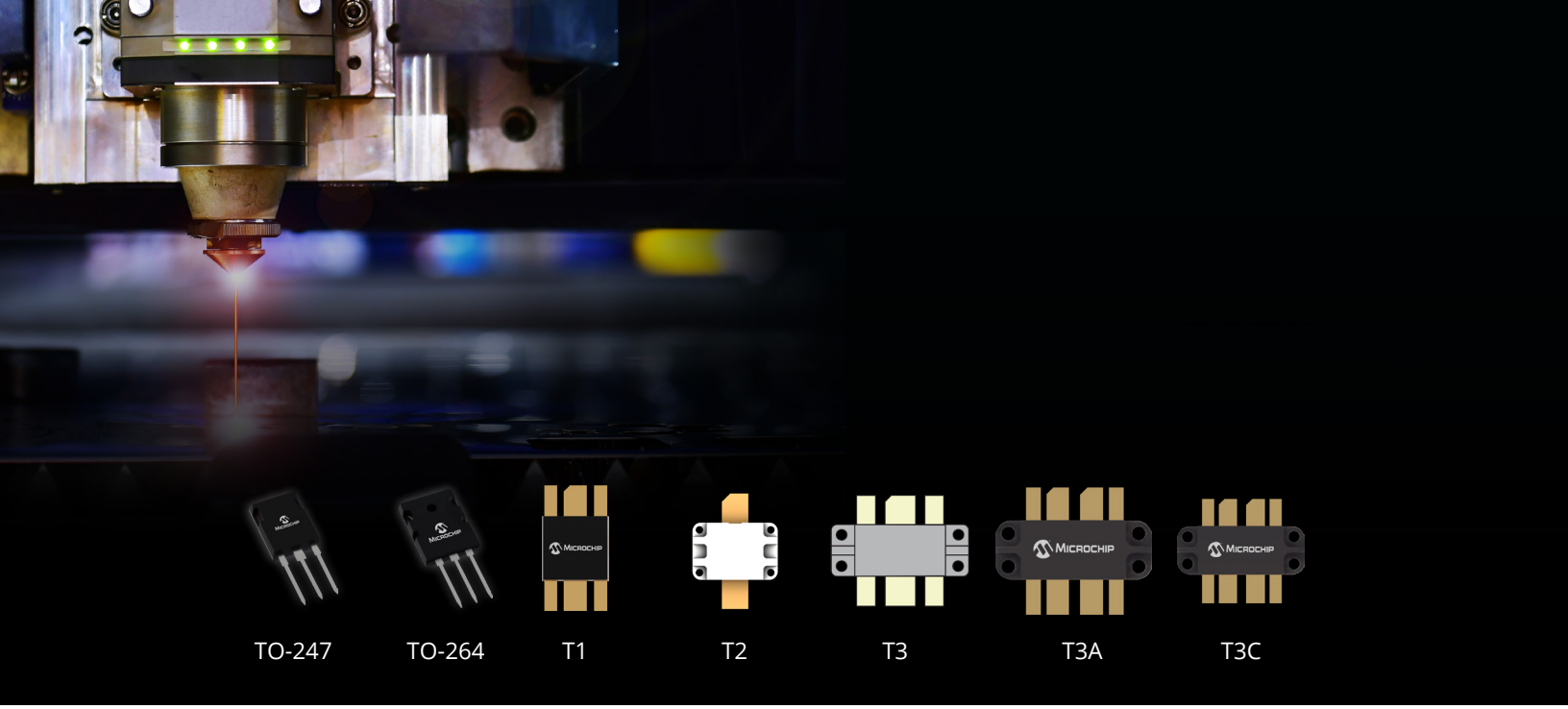
TO-247 [BHB]
Half-bridge



T-MAX® [B2CT]
Common cathode



TO-264 [LCT]
Common cathode



High-Voltage RF MOSFETs

The ARF family of RF power MOSFETs is optimized for applications requiring frequencies as high as 150 MHz and operating voltages as high as 400V. Historically, RF power MOSFETs were limited to applications of 50V or less. This limitation has been removed by combining Microchip's high-voltage MOSFET technology with RF-specific die geometries.

Higher V_{DD} means higher load impedance. For 150W output from a 50V supply, the load impedance is only 8Ω. At 125V, the load impedance is 50Ω. The higher impedance allows simpler transformers and combiners. Paralleled devices can operate into reasonable and convenient impedances. The increased operating voltage also lowers the DC current required for any given power output, increasing efficiency and reducing the size, weight and cost of other system components. High breakdown voltage is a necessity in high-efficiency switchmode amplifiers, such as class C-E, which can see peak drain voltages of over 4x the applied V_{DD}.

Part Number	P_{OUT} (W)	Freq. (MHz)	$V_{DD}/V_{BR(DSS)}$ (V)	Rth_{JC} (°C/W)	Package Style	Class of Operation
ARF460AG/BG	150	65	125/500	0.5	TO-247	A-E
ARF461AG/BG	150	65	250/1000	0.5	TO-247	A-E
ARF463AG/BG	100	100	125/500	0.7	TO-247	A-E
ARF463AP1G/BP1G	100	100	125/500	0.7	TO-247	A-E
ARF465AG/BG	150	60	300/1200	0.5	TO-247	A-E
ARF466AG/BG	300	45	200/1000	0.35	TO-264	A-E
ARF466FL	300	45	200/1000	0.13	T3	A-E
ARF468AG/BG	300	45	150/500	0.35	TO-264	A-E
ARF469AG/BG	350	45	165/500	0.28	TO-264	A-E
ARF475FL	450	128	165/500	0.17	T3A	A-E
ARF476FL	300	128	165/500	0.31	T3C	A-E
ARF477FL	400	100	165/500	0.20	T3C	A-E
ARF1500	750	40	125/500	0.10	T1	A-E
ARF1501	750	40	250/1000	0.10	T1	A-E
ARF1510	750	40	400/1000	0.10	T1A	D
ARF1511	750	40	380/500	0.10	T1A	D
ARF1519	750	25	250/1000	0.13	T2	A-E



High-Frequency RF MOSFETs

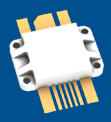
The VRF family of RF MOSFETs includes improved replacements for industry-standard RF transistors. They provide improved ruggedness by increasing the Drain-Source Breakdown Voltage [$V_{BR(DSS)}$] over 30 percent from the industry-standard 125V to 170V minimum. Low-cost flangeless packages are another improvement that shows Microchip's dedication to optimizing performance, reducing cost and improving reliability. We will continue to offer more products with the new reduced-cost flangeless packages.

Part Number	P_{OUT} (W)	Freq. (MHz)	Gain Typ (dB)	Eff. Typ (%)	$V_{DD}/V_{BR(DSS)}$ (V)	Rth_{JC} (°C/W)	Package Style
VRF141	150	175	13	45	28/80	0.60	M174
VRF151	150	175	14	50	20/170	0.60	M174
VRF152	150	175	14	50	50/130	0.60	M174
VRF150	150	150	11	50	50/170	0.60	M174
VRF161	200	150	14	50	50/170	0.50	M174
VRF141G	300	175	14	55	28/80	0.35	M208
VRF151G	300	175	16	55	50/170	0.35	M208
VRF152G	300	175	16	55	50/130	0.35	M208
VRF2933	300	150	22	50	50/170	0.27	M177
VRF2944	400	150	25	50	65/170	0.22	M177
VRF154FL	600	30	17	45	50/170	0.13	T2
VRF157FL	600	30	21	45	50/170	0.13	T2
VRF164FL	600	30	21	45	65/170	0.10	T2

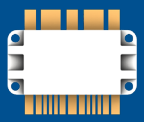
Drivers and Driver-RF MOSFET Hybrids

DRF hybrids provide high efficiency and excellent thermal performance for high power density in a lower cost, more compact system than non-integrated drivers and MOSFETs. The DRF12xx and DRF22xx hybrids integrate drivers, bypass capacitors and RF MOSFETs into a single package. Integration maximizes amplifier performance by minimizing transmission line parasitics between the driver and the MOSFET. The DRF13xx hybrids have two independent channels, each containing a driver and RF MOSFET in a push-pull configuration. The DRF1400 is a half-bridge hybrids with symmetrically oriented leads that can be easily configured into a full-bridge converter. The DRF1510 is a full bridge product optimized for maximum efficiency in class D amplifiers. All DRF parts feature a proprietary anti-ring function to eliminate cross conduction in bridge or push-pull topologies.

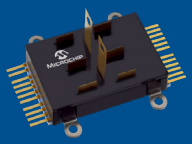
Part Number	P_{OUT} (W)	Freq. (MHz)	$V_{DD}/V_{BR(DSS)}$ (V)	Package Style	Class of Operation
DRF1200	600	30	15/1000	T2B	D-E
DRF1201	1000	30	15/1000	T2B	D-E
DRF1300	1000	30	15/500	T4	D-E
DRF1301	1000	30	15/1000	T4	D-E
DRF1400	1000	30	15/500	T4	D-E
DRF1211	1000	30	15/1000	T2B	D-E
DRF1311	1000	30	15/1000	T4	D-E
DRF1410	1000	30	15/500	T4A	D-E
DRF1510	2000	30	15/500	T102	D-E
DRF2211	1150	30	15/500	T2B	D-E



T2B



T4



T102

RF Reference Design Kits

All kits include a fully populated board attached to an aluminum heat sink, an extensive application note explaining the theory of operation with designer's recommendations for evaluation and board layout, and all key waveforms illustrated and described. A complete parts list with recommended vendor part numbers and the board's Gerber file are provided for an easy transition into an end application.

DRF1200-CLASS-E, 13.56 MHz DRF1200/CLASS-E, 27.12 MHz

The DRF1200-Class-E single-ended reference design allows the designer to evaluate an 85% efficient 1000W Class-E RF generator.

DRF1310-CLASS-D, 13.56 MHz

The DRF1310-CLASS-D push-pull reference design allows the designer to evaluate an 80% efficient 2000W Class-D RF generator.

DRF1400-Class-D, 13.56 MHz

The DRF1400-Class-D half-bridge reference design allows the designer to evaluate an 85% efficient 2500W Class-D RF generator.

DRF1510-CLASS-D, 13.56 MHz

The DRF1510-Class-D full-bridge reference design allows the designer to evaluate a >90% efficient 4500W Class-D RF generator.

mSiC Bare Die

mSiC Bare Die MOSFETs

Part Number	Family	Voltage (V)	$R_{DS(on)}$ (mΩ)	Package
MSC015SMA070D/S 🚗	MA	700	15	Die in Waffle Pack
MSC035SMA070D/S 🚗	MA		35	Die in Waffle Pack
MSC060SMA070D/S 🚗	MA		60	Die in Waffle Pack
MSC090SMA070D/S 🚗	MA		90	Die in Waffle Pack
MSC012SMB120D/S 🚗	MB	1200	12	Die in Waffle Pack
MSC012SMC120D/S 🚗	MC		12	Die in Waffle Pack
MSC016SMC120D/S 🚗	MC		16	Die in Waffle Pack
MSC017SMA120D/S 🚗	MA		17	Die in Waffle Pack
MSC020SMB120D/S 🚗	MB		20	Die in Waffle Pack
MSC025SMB120D/S 🚗	MB		25	Die in Waffle Pack
MSC025SMA120D/S 🚗	MA		25	Die in Waffle Pack
MSC030SMB120D/S 🚗	MB		30	Die in Waffle Pack
MSC031SMC120D/S 🚗	MC		31	Die in Waffle Pack
MSC040SMA120D/S 🚗	MA		40	Die in Waffle Pack
MSC040SMB120D/S 🚗	MB		40	Die in Waffle Pack
MSC045SMB120D/S 🚗	MB		45	Die in Waffle Pack
MSC060SMB120D/S 🚗	MB		60	Die in Waffle Pack
MSC080SMA120D/S 🚗	MA		80	Die in Waffle Pack
MSC080SMB120D/S 🚗	MB		80	Die in Waffle Pack
MSC180SMA120D/S 🚗	MA		180	Die in Waffle Pack
MSC360SMA120D/S 🚗	MA		360	Die in Waffle Pack
MSC750SMA140D/S 🚗	MA	1400	750	Die in Waffle Pack
MSC035SMA170D/S	MA	1700	35	Die in Waffle Pack
MSC750SMA170D/S	MA		750	Die in Waffle Pack
MSC025SMA330D/S	MA	3300	25	Die in Waffle Pack
MSC027SMA330D/S	MA		27	Die in Waffle Pack
MSC080SMA330D/S	MA		80	Die in Waffle Pack
MSC400SMA330D/S	MA		400	Die in Waffle Pack

mSiC Bare Die Diodes

Part number	Family	Voltage (V)	Current (A)	Package
MSC010SDA070D/S 🚗	DA	700	10	Die in Waffle Pack
MSC030SDA070D/S 🚗	DA		30	Die in Waffle Pack
MSC050SDA070D/S 🚗	DA		50	Die in Waffle Pack
MSC010SDA120D/S 🚗	DA	1200	10	Die in Waffle Pack
MSC015SDA120D/S 🚗	DA		15	Die in Waffle Pack
MSC020SDA120D/S 🚗	DA		20	Die in Waffle Pack
MSC030SDA120D/S 🚗	DA		30	Die in Waffle Pack
MSC050SDA120D/S 🚗	DA		50	Die in Waffle Pack
MSC010SDA170D/S	DA	1700	10	Die in Waffle Pack
MSC030SDA170D/S	DA		30	Die in Waffle Pack
MSC050SDA170D/S	DA		50	Die in Waffle Pack
MSC030SDA330D/S	DA	3300	30	Die in Waffle Pack
MSC090SDA330D/S	DA		90	Die in Waffle Pack

Power Modules



Microchip combines a formidable array of technologies in semiconductors, packaging and automated manufacturing to produce a wide range of high-quality modules optimized for the following traits:

- Reliability
- Efficiency and electrical performance
- Low cost
- Space savings
- Reduced assembly time

The readily available standard module product line spans a wide selection of semiconductor (including Silicon Carbide) circuit topologies, voltage and current ratings, and packages. If you need even more flexibility or intellectual property protection, we can customize a standard module with a low setup cost and short lead time. Unique requirements can be met with Application Specific Power Modules (ASPM).

Microchip serves a broad spectrum of industrial applications for welding, solar, induction heating, medical, UPS, motor control and SMPS markets as well as high-reliability applications for semicap, defense and aerospace markets. A wide selection of construction materials enables Microchip to manufacture modules with the following features:

- Extended temperature range: –60°C to 200°C
- High-reliability
- Reduced size and weight
- High-reliability testing and screening options
- Short lead times

Microchip's experience and expertise in power electronic conversion brings the most effective technical support for your new development.

- Isolated gate driver
- Snubbers
- Mix-and-match semiconductors
- Short-circuit protection
- Temperature and current sensing
- Parameter binning

Standard Electrical Configurations

Microchip offers a wide range of standard electrical configurations housed in a variety of packages to match your specific needs for high power-density and performance. Various semiconductor types are offered in the same topology.

Electrical Topology	IGBT 600V–1700V	MOSFET 75V–1200V	Diode 200V–1700V	Mix Si-SiC 600V–1700V	Full SiC 600V–3300V
	Trench 3	MOSFET	FRED	IGBT	Diode
	Trench 4	FREDFET	Std Rectifier	MOSFET	MOSFET
	Trench 4 Fast	Superjunction MOSFET		Diode	
	Trench 5				
	Trench 7				
Active Neutral Point Clamped (ANPC)					•
Asymmetrical bridge	•	•			
Boost buck	•	•			
Boost and buck chopper	•	•		•	•
Common anode			•		
Common cathode			•		
Dual boost and buck chopper	•	•		•	
Dual common source	•	•			•
Dual diode					•
Full bridge	•	•	•		•
Full bridge with PFC	•	•		•	
Full bridge with secondary fast rectifier bridge	•	•		•	
Full bridge with series and parallel diodes		•		•	
Interleaved PFC	•	•			
Linear single and dual switch		•			
Phase leg	•	•	•		•
Phase leg intelligent	•				
Phase leg with PFC		•		•	
Phase leg with series and parallel diodes		•		•	
Single switch	•	•	•		
Single switch with series and parallel diodes		•		•	
Single switch with series diodes	•	•			
3-Level NPC inverter	•				•
3-Level T-Type inverter	•			•	•
3-Phase bridge	•		•		•
Triple dual common source	•	•			
Triple phase leg	•	•		•	•
Vienna rectifier					•

Package Advantages

SP1F package

- Replaces two SOT-227 parts
- Improved assembly time and cost
- Height compatible with SOT-227
- Copper base plate

SP3F package

- Replaces up to four SOT-227 parts
- Reduced assembly time and cost
- Height compatible with SOT-227
- Copper base plate

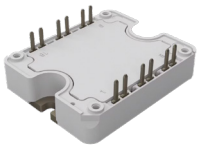
SP6C package

- Offers the same footprint and the same pinout location as the popular 62 mm package but with lower height, giving it the following advantages:
  - Reduced stray inductance
  - Reduced parasitic resistance
  - Higher efficiency at high frequency

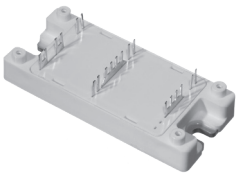
SP6P package

- Replaces up to six SOT-227 parts
- Height compatible with SOT-227
- Low-inductance solder pins
- High current capability

Improved Low-Profile Packages


SP1F


SP3F (12 mm)

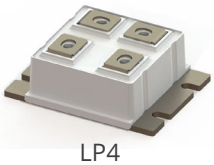

SP4 (17 mm)


D1P (17 mm)


SP6C (17 mm)


SP6P (12 mm)


SP6LI (17 mm)


LP4


SP3X


SP6C-FB


SP6C-HC

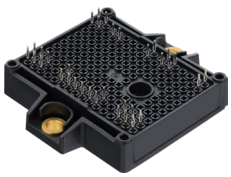

SP6C-3L

Industry-Standard Packages


SOT-227[J]


D3 (62 mm wide)


D4 (62 mm wide)


BZ2


DP3

High Reliability Baseplate-less Packages



BL1 (9.3 mm)



BL2 (9.3 mm)



BL3 (9.3 mm)

Custom Power Modules

Microchip created the Active-state power management (ASPM) concept, and has been offering customized power modules since 1983. We offer a complete engineered solution with mix-and-match capabilities in term of package, configuration, performance and cost.

Internal Printed Circuit Board

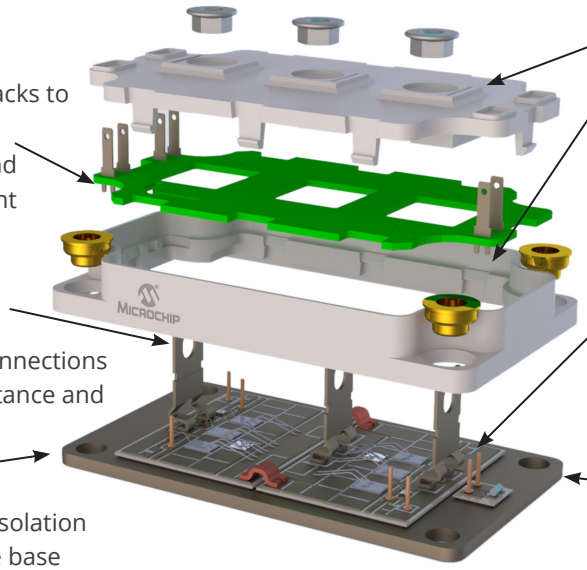
- Not available in all modules
- Used to route gate signals' tracks to small signal terminals
- Used to mount gate circuit and protection in case of intelligent power module

Terminals

- Screw-on or solder pins
- Provides power and signal connections with minimum parasitic resistance and inductance

Substrates

- Al_2O_3, AlN, and Si_3N_4 provide isolation and good heat transfer to the base plate



Package

- Standard or custom
- Ensures environmental protection and mechanical robustness

Power Semiconductor Die

- IGBT, MOSFET, diode, SiC, thyristor and switching devices soldered to the substrates and connected by ultrasonic aluminum wire bonds

Base Plate

- Improves the heat transfer to the heat sink
- Copper for good thermal transfer
- AlSiC, CuW and CuMoCu for improved reliability
- Fin baseplate option

Rugged Custom Versions (Available on Demand):

The standard power module products listed in this catalog are dedicated to industrial applications.

For more severe environmental conditions/requirements, we can propose rugged custom versions (derived from the existing standard products) using specific materials, including Aerospace-grade versions managed under AS9100 Quality Standards, with:

- AlSiC baseplate (instead of copper) for about (6×) higher power cycling capabilities
- Si_3N_4 AMB substrates or AlN DBC substrates (instead of Al_2O_3) for (20%) improved thermal conductivity
- Extended temperature raw materials to address wider temperature range applications (from -60°C Storage ; –55°C to +125°C Operating)

Easy Mounting Solutions With Press-Fit Versions (Available on Demand):

To facilitate the design, the assembly, and repair of your systems, our SP1F and SP3F package type products can be available with Press-Fit terminals.

mSiC MOSFET Modules Without Parallel mSiC Diodes (Available on Demand):

If applicable with your application (for cost saving), the mSiC MOSFET products featuring a parallel mSiC diode, listed in this catalog, can be available without.

Custom Power Modules

The following table shows the three customization levels.

Change Options:	Die	Substrate	Base Plate	Plastic Lid	Terminals	NRE Level	MOQ
Electrical/thermal performance	Die P/N	Material	Material			None to low	5 to 10 pieces
Electrical/thermal performance and electrical configuration	Die P/N	Material and layout	Material			Low to medium	
Electrical/thermal performance, and electrical configuration, and module housing	Die P/N	Material and layout	Material and shape	Material and shape	Shape	Medium to high	

Microchip power modules are made of different sub-elements. Most of them are standard and can be reused to build infinite solutions for the end user. Microchip offers optimum development cost and cycle time thanks to long-term experience and a wide range of available technologies.

Power Modules Features

- High power density
- Isolated and highly thermally-conductive substrate
- Internal wiring
- Minimum parasitics
- Minimum output terminals
- Mix-and-match components
- Fully engineered solutions

Customer Benefits

- Size and cost reduction
- Excellent thermal management
- Reduced external hardware
- Improved performance
- Reduced assembly time
- Optimizes losses
- Easy to upgrade, lower part count, shorter time to market and IP protection

Flexibility

- Great level of integration
- Mix of silicon within the same package
- No quantity limitation

Technology

- Application oriented

Packaging Capability

- Standard and custom packages
- Standard and custom terminals
- Various substrate technologies

Reliability

- Coefficient of thermal expansion matching

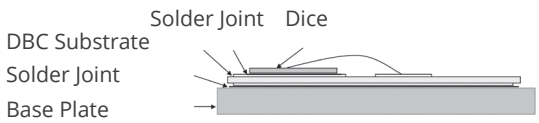
Applications

- Solar, welding, plasma cutting, semicap, MRI and X-ray, EV/HEV, induction heating, UPS, motor control, data communication

Rugged Custom Power Modules

Various proposed solutions offer different costs and low volume of entry

	Industrial Application	Extended Temp. Application	Harsh Environment Application	
Standard module	•			No NRE Low-volume entry
Modified standard module	•	•		Low NRE Low-volume entry
Custom module	•	•	•	Medium to high NRE Low-volume entry





Rugged Custom Power Modules

Microchip has acquired much experience and know-how in module customization that addresses rugged and wide temperature range applications, offering solutions to meet the expectations of next-generation integrated power systems for the following attributes:

- Improved reliability
- Wider operating temperatures
- Higher power
- Higher efficiency
- Lower weight and size
- Lower cost

Applications

- Avionics actuation system
- Avionics lift and pump
- Military ground vehicle
- Power supply and motor control
- Navy ship auxiliary power supply
- Down hole drilling

Test Capabilities

- X-Ray inspection
- Dielectric test (up to 6 kV)
- Electrical testing at specified temperature
- Burn-in
- Acoustic imaging

Reliability Testing Capabilities

- Power cycling
- Hermetic sealing
- Moisture
- Salt atmosphere
- HTGB
- Temperature shock
- HAST
- H3TRB
- HV-H3TRB
- Altitude
- Mechanical shock, vibration

Expertise Capabilities

- Cross-sectioning
- Structural analysis

All tests can be conducted upon demand by sampling or at 100 percent. Tests can be performed in-house or in an external lab.

Our Core Competencies

- Extensive experience with rugged solutions for harsh environments
- Wide range of silicon technologies
- Wafer fab capabilities
- Mix of assembly technologies
- Hermetic and robust plastic packages
- Custom test and burn-in solutions
- ISO9001-certified
- End-of-life (obsolescence) management
- Thermal management
- Material expertise
- Product life management and risk analysis



Module performance and reliability depends on the choice of assembly materials

Temperature Coefficients of Expansion (TCEs) with more closely matched materials increase the module's lifetime by reducing the stress at both the interface and interior of the materials.

The higher the thermal conductivity, the lower the junction-to-case thermal resistance and the lower the delta of junction temperature of the device during operation. This will minimize the effect of power cycling on the dice.

Another important feature is the material density, particularly for the baseplate. Taking copper as the reference, AlSiC has a density of 1/3, while CuW has twice the density. Therefore, AlSiC will provide substantial weight reduction while increasing reliability.

	CTE (ppm/K)	Thermal Conductivity (W/m.K)	RθJC or RTHJC (K/W)
Silicon die (120 mm²)	4	136	
Cu/Al2O3	17/7	390/25	0.35
AlSiC/Al2O3	7/7	170/25	0.38
Cu/AlN	17/5	390/170	0.28
AlSiC/AlN	7/5	170/170	0.31
AlSiC/Si3N4	7/3	170/60	0.31

	Material	CTE (ppm/K) (W/m.K)	Thermal Conductivity	Density (g/cc)
Base plate	CuW AlSiC Cu	6.5 7 17	190 170 390	17 2.9 8.9
Substrate	Al2O3 AlN Si3N4	7 5 3	25 170 60	
Die	Si SiC	4 2.6	136 270	

Power Module Part Numbering System

IGBT Modules

APT MSC	GL	475	A	120	T	D3	G
I	II	III	IV	V	VI	VII	VIII

I TradeMark

II IGBT Type:
GL = Trench 4
GLQ = High-speed Trench 4
GT = Trench 3
GTQ = Trench 5
GV = Mix NPT/Trench
GX = Trench 7
CV = Mix Trench/Superjunction MOSFET

III Current:
I_c at T_c = 80°C

IV Topology:
A = Phase Leg
BB = Boost Buck
DA = Boost Chopper
DDA = Double Boost Chopper
DH = Asymmetrical Bridge
DSK = Double Buck Chopper
DU = Dual Common Source
H = Full Bridge
HR = T-Type 3-level
SDA = Double Boost + Bypass Diode
SK = Buck Chopper
TA = Triple Phase Leg
TDU = Triple Dual Common Source
TL = Three Level
U = Single Switch
VDA = Interleaved PFC
X = Three-phase Bridge

V Blocking Voltage:
60 = 600V
120 = 1200V
170 = 1700V

VI Option:
A = AlN Substrate
C = mSiC Diode
D = Series Diode
E = PressFit
T = Temperature Sensor
W = Clamping Parallel Diode

VII Package:
1 = SP1, SP1F
3 = SP3F
P = SP6P
D3 = D3 (62 mm)
D4 = D4 (62 mm)
BL1, BL2, BL3 (Baseplate-less)

VIII G = RoHS-compliant

MOSFET Modules

APT MSC	C	60	DA	M24	T	1	G
I	II	III	IV	V	VI	VII	VIII

I TradeMark

II MOSFET Type:
SM = mSiC MOSFET
M = MOSFET
C = Superjunction MOSFET

III Blocking Voltage:
08 = 75V
10 = 100V
20 = 200V
50 = 500V
60 = 600V
70 = 700V
80 = 800V
100 = 1000V
120 = 1200V
170 = 1700V

IV Topology:
A = Phase Leg
ANPC = Active Neutral Point Clamped
BB = Boost Buck
DA = Boost Chopper
DDA = Double Boost Chopper
DH = Asymmetrical Bridge
DSK = Double Buck Chopper
DU = Dual Common Source
H = Full Bridge
HR = T-Type 3-Level
SB = D2MAX
SDA = Double Boost and Bypass Diode
SK = Buck Chopper
TA = Triple Phase Leg
TDU = Triple Dual Common Source
TL = Three-level NPC
U = Single Switch
VDA = Interleaved PFC

V $RDS_{(ON)}$ at T_c = 25°C
240 = 2400 mΩ
24 = 240 mΩ
M24 = 24 mΩ

VI Option:
A = AlN Substrate
C = mSiC Diode
D = Series Diode
E = PressFit
F = FREDFET
S = Series and Parallel Diodes
T = Temperature Sensor
U = Ultra-fast FREDFET

VII Package:
1 = SP1, SP1F
3 = SP3F
P = SP6P
LI = SP6LI
BL1, BL2, BL3 (Baseplate-less)

VIII G = RoHS-compliant

Diode Modules

APT MSC	DR	90	X	160	1	G
I	II	III	IV	V	VI	VII

I TradeMark

II Diode Type:
DF = FRED
DR = Standard Rectifier
DC = mSiC Diode
DSK = Schottky

III Current:
I_F at T_c = 80°C

IV Topology:
AA = Dual Common Anode
BB = Boost Buck
AK = Dual Series
KK = Dual Common Cathode
H = Single Phase Bridge
U = Single Switch
X = Three-phase Bridge

V Blocking Voltage:
20 = 200V
40 = 400V
60 = 600V
70 = 700V
100 = 1000V
120 = 1200V
160 = 1600V
170 = 1700V

Option
E = PressFit

VI Package:
1 = SP1, SP1F
3 = SP3F
D1P = D1P
BL1, BL2, BL3 (Baseplate-less)

VII G = RoHS-compliant

Optional Materials

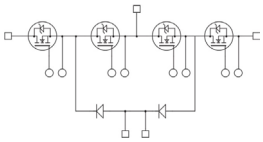
Optional materials are available upon demand for most of the listed standard power modules. Options are indicated with a letter in the suffix of the module part number. The temperature sensor option is listed as “YES” or “OPTION” when available for a standard part or on-demand.

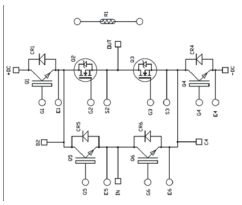
The following tables list the options available for our product categories.

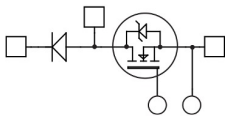
- A AlN substrate for higher thermal conductivity
- M AlSiC base plate material for improved temperature cycling capabilities
- T Temperature sensor (NTC or PTC) for case temperature information
- C mSiC diode for higher efficiency
- N Si_3N_4 substrate
- E Press fit terminals (for SP1F and SP3F package only)
- X Gold pin terminals (SP1F only)
- L Phase change material option

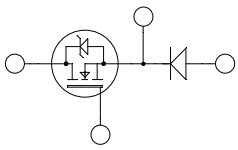
mSiC MOSFET Modules

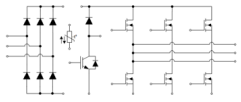
Part Number	Configuration	V_{DSS} (V)	$R_{DS(ON)}$ (mΩ)	Current (A)	Package
MSCSM70TLM05CAG	3 Level Inverter	700	3.8	369	SP6C
MSCSM70TLM07CAG			5	278	SP6C
MSCSM70TLM10C3AG			7.5	191	SP3F
MSCSM70TLM19C3AG			15	98	SP3F
MSCSM70TLM44C3AG			35	46	SP3F
MSCSM120TLM08CAG		1200	6.25	265	SP6C
MSCSM120TLM11CAG			8.3	200	SP6C
MSCSM120TLM16C3AG			12.5	138	SP3F
MSCSM120TLM31C3AG			25	71	SP3F
MSCSM120TLM50C3AG			40	44	SP3F
MSCSM170TLM11CAG		1700	8.8	189	SP6C
MSCSM170TLM15CAG			11.7	142	SP6C
MSCSM170TLM23C3AG			17.5	98	SP3F
MSCSM170TLM45C3AG			35	51	SP3F
MSCSMG120ANPCM11TPAG	Active Neutral Point Clamped	1200	8.4	200	SP6P
MSCSMG170ANPCM15TPAG		1700	11.7	140	SP6P
MSC100SM70JCU2	Boost Chopper	700	15	97	SOT-227
MSCSM120DAM11CT3AG		1200	11	202	SP3F
MSC130SM120JCU2			12.5	138	SOT-227
MSC70SM120JCU2			25	71	SOT-227
MSC40SM120JCU2			40	44	SOT-227
MSC130SMC120JCU2			12.5	155	SOT-227
MSC90SMC120JCU2			18	110	SOT-227
MSC65SMC120JCU2			25	80	SOT-227
MSC100SM70JCU3	Buck Chopper	700	15	97	SOT-227
MSC25SM70JCU3			60	27	SOT-227
MSCSM120SKM11CT3AG		1200	11	202	SP3F
MSC130SM120JCU3			12.5	138	SOT-227
MSC70SM120JCU3			25	71	SOT-227
MSC40SM120JCU3			40	44	SOT-227
MSC130SMC120JCU3			12.5	155	SOT-227
MSC90SMC120JCU3			18	110	SOT-227
MSC65SMC120JCU3			25	80	SOT-227
MSCSM70DUM017AG	Dual Common Source	700	1.7	812	SP6C
MSCSM70DUM025AG			2.5	548	SP6C
MSCSMB120XM60RBTBZ2EG	Converter Inverter Brake	1200	60	25	BZ2
MSCSMC120XM19RBTBZ2EG			35	35	BZ2



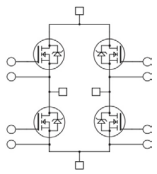




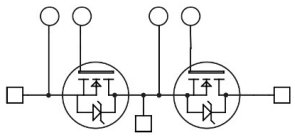




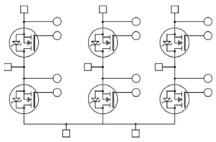
Part Number	Configuration	V_{DSS} (V)	$R_{DS(ON)}$ (mΩ)	Current (A)	Package
MSCSM70DUM07T3AG	Dual Common Source	700	5	281	SP3F
MSCSM70DUM10T3AG			7.5	191	SP3F
MSCSM120DUM027AG		1200	2.8	584	SP6C
MSCSM120DUM042AG			4.2	394	SP6C
MSCSM120DUM08T3AG			6.25	268	SP3F
MSCSM120DUM11T3AG			8.3	202	SP3F
MSCSM120DUM16T3AG			12.5	138	SP3F
MSCSM170DUM039AG	Dual Common Source	1700	3.9	416	SP6C
MSCSM170DUM058AG			5.8	281	SP6C
MSCSM170DUM11T3AG			8.8	191	SP3F
MSCSM170DUM15T3AG			11.6	144	SP3F
MSCSM170DUM23T3AG			17.5	98	SP3F
MSCSM330DUM07D3NG		3300	6.8	234	HV-D3
MSCSM330DUM07CD3NG			6.8	234	HV-D3
MSCSM70HM038AG	Full Bridge	700	3.8	369	SP6C
MSCSM70HM038CAG					SP6C
MSCSM70HM05AG			5	278	SP6C
MSCSM70HM05CAG					SP6C
MSCSM70HM19CT3AG			15	97	SP3F
MSCSM70HM19T3AG				98	SP3F
MSCSM120HM063AG		1200	6.3	265	SP6C
MSCSM120HM063CAG					SP6C
MSCSM120HM083AG			8.3	200	SP6C
MSCSM120HM083CAG					SP6C
MSCSMC120HM19TBZ1EG			19	55	BZ1
MSCSM120HM16T3AG			12.5	138	SP3F
MSCSM120HM16CT3AG					SP3F
MSCSM120HM31T3AG			25	71	SP3F
MSCSM120HM31CT3AG					SP3F
MSCSM120HM50T3AG			40	44	SP3F
MSCSM120HM50CT3AG					SP3F
MSCSM170HM087CAG		1700	8.8	189	SP6C
MSCSM170HM12CAG			11.7	142	SP6C
MSCSM170HM23CT3AG			17.5	98	SP3F
MSCSM170HM45CT3AG			35	51	SP3F

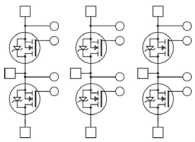


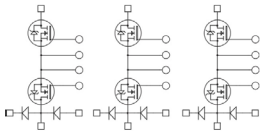
Part Number	Configuration	V_{DSS} (V)	$R_{DS(ON)}$ (mΩ)	Current (A)	Package
MSCSM70AM025CD3AG	Phase Leg	700	2.5	538	D3
MSCSM70AM025CT6AG					SP6C
MSCSM70AM025CT6LIAG					SP6LI
MSCSM70AM025D3AG				548	D3
MSCSM70AM025T6AG					SP6C
MSCSM70AM025T6LIAG					SP6LI
MSCSM70AM07CT3AG			5	276	SP3F
MSCSM70AM07T3AG				281	SP3F
MSCSM70AM10CT3AG			7.5	188	SP3F
MSCSM70AM10T3AG				192	SP3F
MSCSM70AM19CT1AG			15	97	SP1F
MSCSM70AM19T1AG				98	SP1F
MSCSM120AM02T6LIAG		1200	2.1	754	SP6LI
MSCSM120AM02CT6LIAG					SP6LI
MSCSM120AM03T6LIAG			2.5	640	SP6LI
MSCSM120AM03CT6LIAG				641	SP6LI
MSCSM120AM027CD3AG			2.7	584	D3
MSCSM120AM027CT6AG					SP6C
MSCSMC120AM04TBZ2EG			4	726	BZ2
MSCSMC120AM04TBZ2AEG					BZ2
MSCSM120AM027D3AG			2.8	584	D3
MSCSM120AM027T6AG					SP6C
MSCSM120AM042CD3AG			4.2	394	D3
MSCSM120AM042CT6AG					SP6C
MSCSM120AM042CT6LIAG					SP6LI
MSCSM120AM042D3AG				395	D3
MSCSM120AM042T6AG					SP6C
MSCSM120AM042T6LIAG					SP6LI
MSCSM120AM08CT3AG			6.25	268	SP3F
MSCSM120AM08T3AG			6.3		SP3F
MSCSM120AM11CT3AG			8.33	202	SP3F
MSCSM120AM11T3AG			8.4		SP3F
MSCSM120AM16T1AG			12.5	138	SP1F
MSCSM120AM16CT1AG					SP1F
MSCSM120AM31T1AG			25	71	SP1F
MSCSM120AM31CT1AG					SP1F
MSCSM120AM50T1AG			40	44	SP1F
MSCSM120AM50CT1AG					SP1F

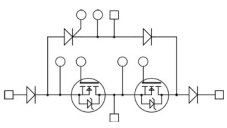


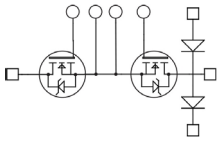
Part Number	Configuration	V_{DSS} (V)	$R_{DS(ON)}$ (mΩ)	Current (A)	Package
MSCSM170AM029CT6LIAG	Phase Leg	1700	2.9	538	SP6LI
MSCSM170AM039CD3AG			3.9	416	D3
MSCSM170AM039CT6AG					SP6C
MSCSM170AM058CD3AG			5.8	281	D3
MSCSM170AM058CT6AG					SP6C
MSCSM170AM058CT6LIAG					SP6LI
MSCSM170AM11CT3AG			8.8	191	SP3F
MSCSM170AM15CT3AG			11.7	144	SP3F
MSCSM170AM23CT1AG			17.5	98	SP1F
MSCSM170AM45CT1AG			35	51	SP1F
MSCSM330AM15D3NG			13.5	120	HV-D3
MSCSM330AM15CD3NG					HV-D3
MSCSM330AM07D3NG			6.7	234	HV-D3
MSCSM330AM07CD3NG			6.8		HV-D3
MSCSMC120XM14TBZ2AEG	Six-Pack	1200	14	72	BZ2
MSCSMC120XM14TBZ2EG					BZ2
MSCSMC120XM19TBZ1EG			19	55	
MSCSMC120XM19TBZ1AEG					
MSCSM120TAM31CT3AG	Three-phase Bridge	1200	25	71	SP3F
MSCSM70TAM05TPAG	Triple Phase Leg	700	5	273	SP6P
MSCSM70TAM10CTPAG			7.5	186	SP6P
MSCSM70TAM10TPAG			15	189	SP6P
MSCSM70TAM19CT3AG				97	SP3F
MSCSM70TAM19T3AG				98	SP3F
MSCSM120TAM11CTPAG		1200	8.33	200	SP6P
MSCSM120TAM11TPAG			8.4	200	SP6P
MSCSM120TAM16TPAG			12.5	136	SP6P
MSCSM120TAM16CTPAG			25	71	SP6P
MSCSM120TAM31T3AG					SP3F
MSCSM170TAM15CTPAG		1700	11.7	142	SP6P
MSCSM170TAM23CTPAG			17.5	97	SP6P
MSCSM170TAM45CT3AG			35	51	SP3F
MSCSM70VR1M10CTPAG	Triple Vienna Rectifier	700	7.5	189	SP6P
MSCSM120VR1M16CTPAG		1200	12.5	136	SP6P







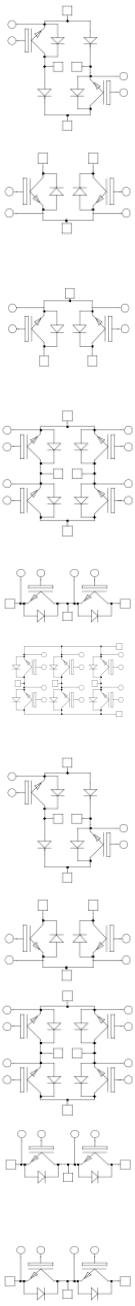




Part Number	Configuration	V_{DSS} (V)	$R_{DS(ON)}$ (mΩ)	Current (A)	Package
MSCSM120HRM052NG	T-Type	1200	4.2	376	SP6C
MSCSM120HRM08NG			6.3	252	SP6C
MSCSM120HRM163AG			12.5	138	SP3F
MSCSM120HRM311AG			25	71	SP1F
MSCSM170HRM075NG		1700	5.8	268	SP6C
MSCSM170HRM11NG			8.8	180	SP6C
MSCSM170HRM233AG			17.5	98	SP3F
MSCSM170HRM451AG			35	51	SP1F
MSCSM70VM10C4AG	Vienna Phase Leg	700	7.5	97	SP4
MSCSM70VM19C3AG			15	97	SP3F
MSCSM70VR1M03CT6AG	Vienna Rectifier	700	3	465	SP6C
MSCSM70VR1M07CT6AG			5	278	SP6C
MSCSM70VR1M10CT3AG			7.5	192	SP3F
MSCSM70VR1M19C1AG			15	98	SP1F
MSCSM120VR1M062CT6AG		1200	5	334	SP6C
MSCSM120VR1M11CT6AG			8.3	200	SP6C
MSCSM120VR1M16CT3AG			12.5	138	SP3F
MSCSM120VR1M31C1AG			25	71	SP1F

Baseplate-less mSiC MOSFET Modules

Part Number	Configuration	V_{DSS} (V)	$R_{DS(ON)}$ (mΩ)	Current (A)	Package
MSCSM120DHM31CTBL2NG	Asymmetrical Bridge	1200	25	60	BL2
MSCSM120DAM31CTBL1NG	Boost Chopper	1200	25	60	BL1
MSCSM120SKM31CTBL1NG	Buck Chopper	1200	25	60	BL1
MSCSM120DDUM16TBL3NG	Double Dual Common Source	1200	12.5	120	BL3
MSCSM120DDUM31CTBL2NG			25	60	BL2
MSCSM120DDUM31TBL2NG				63	BL2
MSCSM120DDUM16CTBL3NG	Dual Common Source	1200	12.5	120	BL3
MSCSM120DUM31CTBL1NG			25	60	BL1
MSCSM120DUM31TBL1NG				63	BL1
MSCSM120HM16TBL3NG	Full Bridge	1200	12.5	120	BL3
MSCSM120HM16CTBL3NG					BL3
MSCSM120HM31CTBL2NG			25	60	BL2
MSCSM120HM31TBL2NG				63	BL2
MSCSMC120HM08TBZ2AEG			8	140	BZ2
MSCSMC120HM08TBZ2EG			8	140	BZ2
MSCSMC120HM14TBZ2AEG			14	72	BZ2
MSCSMC120HM14TBZ2EG			14	72	BZ2
MSCSM120AM31CTBL1NG	Phase Leg	1200	25	60	BL1
MSCSM120AM31TBL1NG				63	BL1
MSCSMC120AM04TBZ2AEG			4	230	BZ2
MSCSMC120AM04TBZ2EG			4	140	BZ2
MSCSMC120AM08TBZ2AEG			8	159	BZ2
MSCSMC120AM08TBZ2EG			8	159	BZ2
MSCSM120XM31RTBL3NG	Three-phase Bridge	1200	25	63	BL3



Baseplate-less Si IGBT Power Modules

Part Number	Silicon type	Configuration	V_{CE} (V)	$V_{CE(sat)}$ (V)	Current (A) Tc=80 C	Package
MSCGLQ50DH120CTBL2NG	Trench 4 Fast	Asymmetrical bridge	1200	2.05	50	BL2
MSCGLQ50DU120CTBL1NG	Trench 4 Fast	Dual common source		2.05	50	BL1
MSCGLQ50DDU120CTBL2NG	Trench 4 Fast	Dual common source		2.05	50	BL2
MSCGLQ75DDU120CTBL3NG	Trench 4 Fast	Dual common source		2.05	75	BL3
MSCGLQ50H120CTBL2NG	Trench 4 Fast	Full bridge		2.05	50	BL2
MSCGLQ75H120CTBL3NG	Trench 4 Fast	Full bridge		2.05	75	BL3
MSCGLQ50A120CTBL1NG	Trench 4 Fast	Phase leg		2.05	50	BL1

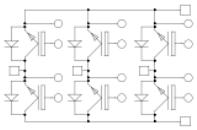
Baseplate-less Si Diode Power Modules

Part Number	Silicon Type	Configuration	V_{RRM} (V)	V_F (V)	Current (A) Tc=80 C	Package
MSCDR90A160BL1NG	Rectifier diode	Phase leg	1600	1.3	90	BL1

Standard Aerospace Power Modules

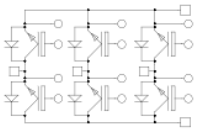
mSiC MOSFET Power Modules

Part Number	Type	Electrical Topology	Voltage	$R_{DS(on)}$ (mΩ)	Current (A) Tc=80°C	Package
MSCSM70XM75CTYZBNMG	mSiC MOSFET Module	3 Phase Bridge + Actuation Full-Options	700	60	25	SP6HPD
MSCSM70XM45CTYZBNMG				35	45	SP6HPD
MSCSM70XM19CTYZBNMG				15	89	SP6HPD
MSCSM120X10CTYZBNMG			1200	80	22	SP6HPD
MSCSM120XM50CTYZBNMG				40	40	SP6HPD
MSCSM120XM31CTYZBNMG				25	64	SP6HPD
MSCSMC120XM047CT7NMG				6	271	SP7HPD



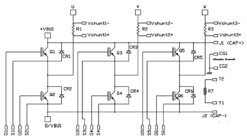
IGBT Power Modules with mSiC Diodes

Part Number	Type	Electrical Topology	Voltage	$V_{CE(sat)}$ (V)	Current (A) Tc=80°C	Package
MSCGLQ50X065CTYZBNMG	Trench 4 Fast IGBT + SiC SBD	3 Phase Bridge + Actuation Full-Options	650	1.85	50	SP6HPD
MSCGLQ75X065CTYZBNMG					75	SP6HPD
MSCGLQ100X065CTYZBNMG					100	SP6HPD
MSCGLQ40X120CTYZBNMG			1200	2.05	40	SP6HPD
MSCGLQ50X120CTYZBNMG					50	SP6HPD
MSCGLQ75X120CTYZBNMG					75	SP6HPD
MSCSMC120XM047CT7NMG				1.8	150	SP7HPD



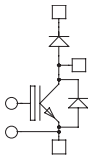
IGBT Power Modules

Part Number	Type	Electrical Topology	Voltage	$V_{CE(sat)}$ (V)	Current (A) Tc=80 C	Package
APTGX150X120T7NMG	Trench 4 Fast IGBT	3 Phase Bridge + Actuation Full Options	1200	1.8	150	SP7HPD



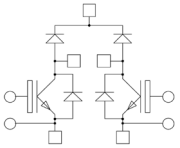
IGBT & Si MOSFET Power Modules with mSiC Diodes

Boost Chopper



V_{RRM} (V)	IGBT Type	I_D (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
1200	Trench 4 Fast	25	2.05	SOT-227	No	APT25GLQ120JCU2
		40	2.05	SOT-227	No	APT40GLQ120JCU2

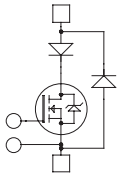
Dual Chopper



V_{RRM} (V)	IGBT Type	I_D (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
1200	Trench 4 Fast	40	2.05	SP3F	Yes	APTGLQ40DDA120CT3G

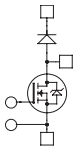
MOSFETs and Superjunction MOSFET Power Modules With mSiC Diodes

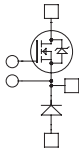
Single Switch Series and Parallel mSiC Diodes



V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
1000	MOS 7™	65	110	SP6C Resin	Option	APTM100UM65SCAVG
1200	MOS 7	100	86	SP6C Resin	Option	APTM120U10SCAVG

Power Modules With mSiC Diodes

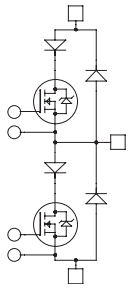




Chopper

V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	...DA... or ...U2	...SK... or ...U3
500	MOS 8	65	43	SOT-227	No	APT58M50JCU2	
600	Superjunction MOSFET	45	38	SOT-227	No	APT50N60JCCU2	
		24	70	SP1F	Yes		APTC60SKM24CT1G
1000	MOS 8	330	20	SOT-227	No	APT26M100JCU2	APT26M100JCU3
1200	MOS 8	560	15	SOT-227	No	APT20M120JCU2	APT20M120JCU3
		300	23	SP1F	Yes	APTM120DA30CT1G	

Phase Leg Series and Parallel mSiC Diodes

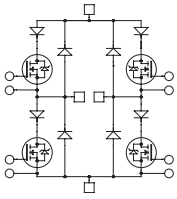


V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
500	MOS 7	38	67	SP4	Yes	APTM50AM38SCTG
		24	110	SP6C	No	APTM50AM24SCG
600	Superjunction MOSFET	24	70	SP4	Yes	APTC60AM24SCTG
1000	MOS 7	130	49	SP6C	No	APTM100A13SCG



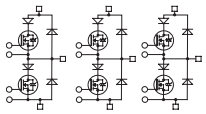
Full Bridge Series and Parallel mSiC Diodes

V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
500	MOS 7™	75	34	SP4	Yes	APTM50HM75SCTG
600	Superjunction MOSFET	45	38	SP4	Yes	APTC60HM45SCTG
1000	MOS 7	450	14	SP4	Yes	APTM100H45SCTG

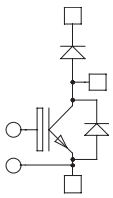
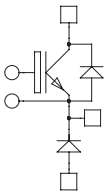
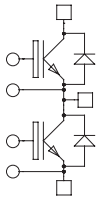


Triple Phase Leg

V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
600	Superjunction MOSFET	24	87	SP6P	Yes	APTC60TAM21SCTPAG
1000	MOS 7	350	50	SP6P	Yes	APTM100TA35SCTPG

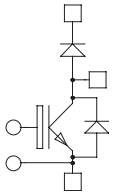
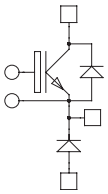
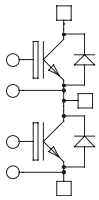


IGBT Power Modules

Chopper and Phase Leg

$V_{(BR)CES}$ (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	...DA... or ...U2	...SK... or ...U3	...A...
600	Trench 3	75	1.5	SP1F	YES	APTGT75DA60T1G		APTGT75A60T1G
		100	1.5	SP1F	YES	APTGT100DA60T1G		APTGT100A60T1G
		150	1.5	SP1F	YES	APTGT150DA60T1G	APTGT150SK60T1G	APTGT150A60T1G
		150	1.5	SP3F	YES			APTGT150A60T3AG
		200	1.5	SP3F	YES	APTGT200DA60T3AG	APTGT200SK60T3AG	APTGT200A60T3AG
		300	1.5	SP4	YES			APTGT300A60TG
		300	1.5	SP6C	OPTION	APTGT300DA60G	APTGT300SK60G	APTGT300A60G
		300	1.5	D3	OPTION	APTGT300DA60D3G	APTGT300SK60D3G	APTGT300A60D3G
		400	1.5	D3	OPTION	APTGT400DA60D3G		APTGT400A60D3G
		450	1.5	SP6C	OPTION	APTGT450DA60G	APTGT450SK60G	APTGT450A60G
		600	1.5	SP6C	OPTION	APTGT600DA60G	APTGT600SK60G	APTGT600A60G
650	Trench 4 Fast	50	1.85	SOT227		APT50GLQ65JU2		
		50	1.85	SOT227		APT100GLQ65JU2	APT100GLQ65JU3	
		100	1.85	SP1F	YES			APTGLQ100A65T1G
		600	1.85	SP6C	YES			APTGLQ600A65T6G
	Trench 5	60	1.65	SP1F	YES	APTGTQ100DA65T1G	APTGTQ100SK65T1G	APTGTQ100A65T1G
		120	1.65	SP3F	YES	APTGTQ200DA65T3G	APTGTQ200SK65T3G	APTGTQ200A65T3G
1200	Trench 3	35	1.7	SP1F	YES			APTGT35A120T1G
		35	1.7	SOT227	–	APT35GT120JU2	APT35GT120JU3	
		50	1.7	SOT227	–	APT50GT120JU2	APT50GT120JU3	
		50	1.7	SP1F	YES			APTGT50A120T1G
		50	1.7	SP4	YES	APTGT50DA120TG	APTGT50SK120TG	
		75	1.7	SOT227	–	APT75GT120JU2	APT75GT120JU3	
		75	1.7	SP1F	YES			APTGT75A120T1G
		75	1.7	SP4	YES	APTGT75DA120TG	APTGT75SK120TG	
		100	1.7	SP1F	YES	APTGT100DA120T1G		
		100	1.7	SOT227	–	APT100GT120JU2	APT100GT120JU3	
		100	1.7	SP3F	YES			APTGT100A120T3AG
		100	1.7	SP4	YES			APTGT100A120TG
		150	1.7	SP6C	OPTION	APTGT150DA120G	APTGT150SK120G	APTGT150A120G
		150	1.7	SP3F	YES			APTGT150A120T3AG
		150	1.7	SP4	YES			APTGT150A120TG
		200	1.7	SP6C	OPTION	APTGT200DA120G	APTGT200SK120G	APTGT200A120G
		200	1.7	D3	OPTION	APTGT200DA120D3G		APTGT200A120D3G
		300	1.7	SP6C	OPTION	APTGT300DA120G	APTGT300SK120G	APTGT300A120G
		300	1.7	D3	OPTION			APTGT300A120D3G
		400	1.7	SP6C	OPTION	APTGT400DA120G	APTGT400SK120G	APTGT400A120G
		400	1.7	D3	OPTION			APTGT400A120D3G
	Trench 4	40	1.85	SOT227	–	APT40GL120JU2	APT40GL120JU3	
		90	1.85	SP1F	YES	APTGL90DA120T1G		APTGL90A120T1G
		180	1.85	SP3F	YES			APTGL180A120T3AG
		325	1.85	D3	OPTION			APTGL325A120D3G
		475	1.85	D3	OPTION	APTGL475DA120D3G	APTGL475SK120D3G	APTGL475A120D3G
		700	1.85	D3	OPTION	APTGL700DA120D3G	APTGL700SK120D3G	

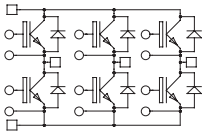




Chopper and Phase Leg

$V_{(BR)CES}$ (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	...DA... or ...U2	...SK... or ...U3	...A...
1200	Trench 4 Fast	100	2.05	SP3F	YES			APTGLQ100A120T3AG
		100	2.05	SP1F	YES	APTGLQ100DA120T1G		
		100	2.05	SP4	YES			APTGLQ100A120TG
		150	2.05	SP4	YES			APTGLQ150A120TG
		200	2.05	SP3F	YES			APTGLQ200A120T3AG
		300	2.05	SP6C			APTGLQ300SK120G	APTGLQ300A120G
		400	2.05	SP6C	YES			APTGLQ400A120T6G
	Trench 7	600	1.55	SP6C		APTGX600DA120T6G		
		600	1.55	SP6C			APTGX600SK120T6G	
		100	1.55	SP1F				APTGX100A120T1G
		200	1.55	SP3F				APTGX200A120T3AG
		300	1.55	D3				APTGX300A120D3G
		300	1.55	SP6C				APTGX300A120T6G
		300	1.55	SP6LI				APTGX300A120T6LIAG
		400	1.55	D3				APTGX400A120D3G
		450	1.55	SP6C				APTGX450A120T6G
		450	1.55	SP6LI				APTGX450A120T6LIAG
		600	1.55	D3				APTGX600A120D3G
		600	1.55	SP6C				APTGX600A120T6G
		600	1.55	SP6LI				APTGX600A120T6LIAG
		75	1.55	SP1F				APTGX75A120T1G
1700	Trench 3	30	2	SP1F	YES			APTGT30A170T1G
		50	2	SP1F	YES		APTGT50SK170T1G	APTGT50A170T1G
		50	2	SP4	YES		APTGT50SK170TG	APTGT50A170TG
		100	2	SP4	YES		APTGT100SK170TG	APTGT100A170TG
		150	2	SP6C	OPTION		APTGT150SK170G	
		200	2	D3	OPTION			APTGT200A170D3G
		225	2	SP6C	OPTION		APTGT225SK170G	APTGT225A170G
		300	2	SP6C	OPTION	APTGT300DA170G	APTGT300SK170G	APTGT300A170G
		300	2	D3	OPTION	APTGT300DA170D3G		APTGT300A170D3G

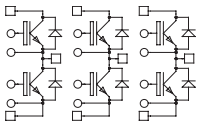
Three-phase Bridge

$V_{(BR)CES}$ (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
600	Trench 3	30	1.5	SP3F	Yes	APTGT30X60T3G
		50	1.5	SP3F	Yes	APTGT50X60T3G
		75	1.5	SP3F	Yes	APTGT75X60T3G
1200	Trench 3	25	1.7	SP3F	Yes	APTGT25X120T3G
		35	1.7	SP3F	Yes	APTGT35X120T3G
	Trench 4	40	1.85	SP3F	Yes	MSCGL40X120T3AG
		40	1.85	SP3F	Yes	APTGL40X120T3G



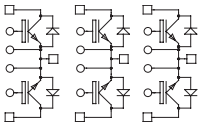
Triple Phase Leg

$V_{(BR)CES}$ (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
600	Trench 3	50	1.5	SP6P	Option	APTGT50TA60PG
		150	1.5	SP6P	Option	APTGT150TA60PG
650	Trench 5	30	1.65	SP3F	Yes	APTGTQ50TA65T3G
		90	1.65	SP6P	Yes	APTGTQ150TA65TPG
1200	Trench 3	75	1.7	SP6P	Option	APTGT75TA120PG
		100	1.7	SP6P	Yes	APTGT100TA120TPG
	Trench 4	120	1.85	SP6P	Yes	APTGL120TA120TPG
	Trench 7	150	1.55	SP6P		APTGX150TA120TPG
		50	1.55	SP3F		APTGX50TA120T3AG



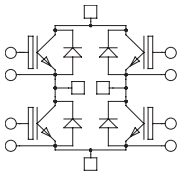
Triple Dual Common Source

$V_{(BR)CES}$ (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
600	Trench 3	50	1.5	SP6P	Option	APTGT50TDU60PG
		75	1.5	SP6P	Option	APTGT75TDU60PG
		100	1.5	SP6P	Option	APTGT100TDU60PG
		150	1.5	SP6P	Option	APTGT150TDU60PG
1200	Trench 3	75	1.7	SP6P	Option	APTGT75TDU120PG
	Trench 4	120	1.85	SP6P	Yes	APTGL120TDU120TPG
1700	Trench 3	50	2	SP6P	Option	APTGT50TDU170PG

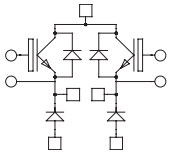


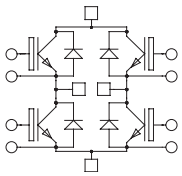
Dual Chopper

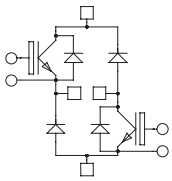
$V_{(BR)CES}$ (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	...DDA...	...DSK...
600	Trench 3	50	1.5	SP3F	Yes	APTGT50DDA60T3G	
		75	1.5	SP3F	Yes	APTGT75DDA60T3G	
650	Trench 5	60	1.65	SP3F	Yes	APTGTQ100DDA65T3G	
	Trench 4 Fast	50	1.85	SP3F	Yes	APTGLQ50DDA65T3G	
	Trench 4 Fast	50	1.85	SP3F	Yes	APTGLQ50VDA65T3G	
1200	Trench 3	50	1.7	SP3F	Yes	APTGT50DDA120T3G	
	Trench 4	60	1.85	SP3F	Yes	APTGL60DDA120T3G	
		90	1.85	SP3F	Yes	APTGL90DDA120T3G	APTGL90DSK120T3G



DDA







Full and Asymmetrical

$V_{(BR)CES}$ (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	...H...	...DH...
600	Trench 3	20	1.5	SP1F	YES	APTGT20H60T1G	
		30	1.5	SP1F	YES	APTGT30H60T1G	
		50	1.5	SP1F	YES	APTGT50H60T1G	APTGT50DH60T1G
		50	1.5	SP3F	YES	APTGT50H60T3G	
		75	1.5	SP1F	YES	APTGT75H60T1G	
		75	1.5	SP3F	YES	APTGT75H60T3G	
		100	1.5	SP4	YES	APTGT100H60TG	APTGT100DH60TG
		100	1.5	SP3F	YES	APTGT100H60T3G	
		150	1.5	SP4	YES	APTGT150H60TG	APTGT150DH60TG
		200	1.5	SP6C		APTGT200H60G	APTGT200DH60G
		300	1.5	SP6C		APTGT300H60G	APTGT300DH60G
650	Trench 4 Fast	30	1.95	SP3F	YES	APTGLQ30H65T3G	
		50	1.85	SP1F	YES	APTGLQ50H65T1G	
		50	1.85	SP3F	YES	APTGLQ50H65T3G	
		75	1.85	SP1F	YES	APTGLQ75H65T1G	
		100	1.85	SP3F	YES	APTGLQ100H65T3G	
		200	1.85	SP6C		APTGLQ200H65G	
		300	1.85	SP6C	OPTION	APTGLQ300H65G	
	Trench 5	60	1.65	SP3F	YES	APTGTQ100H65T3G	
1200	Trench 3	35	1.7	SP3F	YES	APTGT35H120T3G	
		50	1.7	SP3F	YES	APTGT50H120T3G	
		50	1.7	SP4	YES		APTGT50DH120TG
		75	1.7	SP3F	YES		APTGT75DH120T3G
		75	1.7	SP4	YES	APTGT75H120TG	
		100	1.7	SP4	YES		APTGT100DH120TG
		100	1.7	SP6C		APTGT100H120G	
		150	1.7	SP6C		APTGT150H120G	APTGT150DH120G
		200	1.7	SP6C		APTGT200H120G	APTGT200DH120G
	Trench 4	40	1.85	SP1F	YES	APTGL40H120T1G	
		60	1.85	SP3F	YES	APTGL60H120T3G	
		90	1.85	SP3F	YES	APTGL90H120T3G	
	Trench 4 Fast	25	2.05	SP1F	YES	APTGLQ25H120T1G	
		40	2.05	SP1F	YES	APTGLQ40H120T1G	
		75	2.05	SP3F	YES	APTGLQ75H120T3G	
		75	2.05	SP4	YES	APTGLQ75H120TG	
		150	2.05	SP6C		APTGLQ150H120G	
		200	2.05	SP6C	OPTION	APTGLQ200H120G	
	Trench 7	100	1.55	SP3F		APTGX100H120T3G	
		200	1.55	SP6C		APTGX200H120G	
		300	1.55	SP6C		APTGX300H120G	
		50	1.55	SP1F		APTGX50H120T1G	
1700	Trench 3	30	2	SP3F	YES	APTGT30H170T3G	
		50	2	SP4	YES	APTGT50H170TG	APTGT50DH170TG
		100	2	SP6C		APTGT100H170G	
		150	2	SP6C			APTGT150DH170G

Dual Common Emitter

VBRCES (V)	IGBT Type	Module Type	VCEon (V) (Trench)	Current (A)@ Tc=80°C	Part Number	PKG
1200	Trench 7	IGBT	1.55	100	APTGX100DU120T3AG	SP3F
		IGBT	1.55	150	APTGX150DU120T3AG	SP3F
		IGBT	1.55	200	APTGX200DU120T3AG	SP3F
		IGBT	1.55	300	APTGX300DU120T6G	SP6C
		IGBT	1.55	450	APTGX450DU120T6G	SP6C
		IGBT	1.55	600	APTGX600DU120T6G	SP6C

Three-level inverter

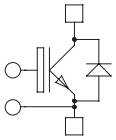
VBRCES (V)	IGBT Type	Module Type	VCEon (V) (Trench)	Current (A)@ Tc=80°C	Part Number	PKG
1200	Trench 7	IGBT	1.55	300	APTGX300TL120G	SP6C

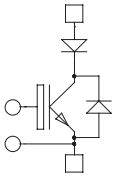
T-Type

VBRCES (V)	IGBT Type	Module Type	VCEon (V) (Trench)	Current (A)@ Tc=80°C	Part Number	PKG
1200	Trench 7	IGBT	1.55	300	APTGX300HR120G	SP6C

Single Switch

V_{CES} (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
600	Trench 3	750	1.5	D4	No	APTGT750U60D4G
1200	Trench 3	400	1.7	D4	No	APTGT400U120D4G
		600	1.7	D4	No	APTGT600U120D4G
	Trench 4	475	1.85	D4	No	APTGL475U120D4G
		700	1.85	D4	No	APTGL700U120D4G
	Trench 7	600	1.55	D4		APTGX600U120D4G
		800	1.55	D4		APTGX800U120D4G
1700	Trench 3	400	2	D4	No	APTGT400U170D4G
		600	2	D4	No	APTGT600U170D4G



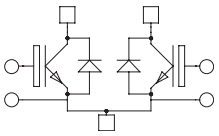


Single Switch + Series Diode

V_{CES} (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
1200	Trench 4	475	1.85	SP6C	No	APTGL475U120DAG

Dual Common Source

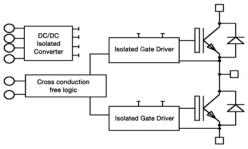
V_{CES} (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
600	Trench 3	100	1.5	SP4	Yes	APTGT100DU60TG
		200	1.5	SP4	Yes	APTGT200DU60TG
		300	1.4	SP6C	No	APTGT300DU60G
		600	1.4	SP6C	No	APTGT600DU60G
1200	Trench 3	50	1.7	SP4	Yes	APTGT50DU120TG
		75	1.7	SP4	Yes	APTGT75DU120TG
		100	1.7	SP4	Yes	APTGT100DU120TG
		150	1.7	SP6C	No	APTGT150DU120G
		150	1.7	SP4	Yes	APTGT150DU120TG
		200	1.7	SP6C	No	APTGT200DU120G
		300	1.7	SP6C	No	APTGT300DU120G
		400	1.7	SP6C	No	APTGT400DU120G
1700	Trench 3	100	2	SP4	Yes	APTGT100DU170TG
		225	2	SP6C	No	APTGT225DU170G
		300	2	SP6C	No	APTGT300DU170G



Intelligent Power Modules

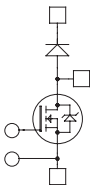
Phase Leg

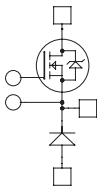
Vces (V)	IGBT Type	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
600	Trench 3	400	1.5	LP8	No	APTLGT400A608G
1200	Trench 3	300	1.7	LP8	No	APTLGT300A1208G
	Trench 4	325	1.8	LP8	No	APTLGL325A1208G



MOSFET Power Modules

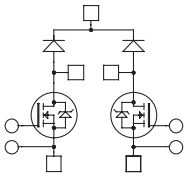
Chopper

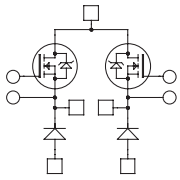




V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	DA...or...U2	SK...or...U3
100	MOS 5	11	100	SOT-227	No	APT10M11JVRU2	APT10M11JVRU3
		4.5	207	SP4	Yes	APTM10DAM05TG	APTM10SKM05TG
		2.25	370	SP6C	No	APTM10DAM02G	APTM10SKM02G
200	MOS 5	22	71	SOT-227	No	APT20M22JVRU2	APT20M22JVRU3
	MOS 7™	8	147	SP4	Yes	APTM20DAM08TG	APTM20SKM08TG
		5	250	SP6C	Option	APTM20DAM05G	
		4	300	SP6C	Option	APTM20DAM04G	APTM20SKM04G
500	MOS 5	100	30	SOT-227	No	APT5010JVRU2	APT5010JVRU3
	MOS 7	100	30	SOT-227	No	APT5010JLLU2	APT5010JLLU3
		75	32	SOT-227	No	APT50M75JLLU2	APT50M75JLLU3
		19	125	SP6C	Option	APTM50DAM19G	APTM50SKM19G
		17	140	SP6C	Option	APTM50DAM17G	APTM50SKM17G
	MOS 8™	65	43	SOT-227	No	APT58M50JU2	APT58M50JU3
600	Superjunction MOSFET	24	70	SP1F	Yes		APTC60SKM24T1G
1000	MOS 7	180	33	SP4	Yes	APTM100DA18TG	
		90	59	SP6C	Option	APTM100DAM90G	
	MOS 8	330	17	SP1F	Yes		APTM100SK33T1G
1200	MOS 8	300	23	SP1F	Yes	APTM120DA30T1G	

Dual Chopper

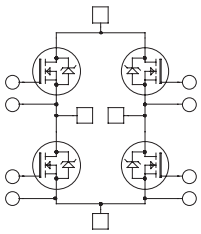




V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	...DDA...	...DSK...
100	MOS 5	19	50	SP3F	Yes		APTM10DSKM19T3G
		9	100	SP3F	Yes		APTM10DSKM09T3G
500	MOS 7	100	24	SP3F	Yes	APTM50DDA10T3G	
		65	37	SP3F	Yes	APTM50DDAM65T3G	
600	Superjunction MOSFET	45	38	SP1F	Yes	APTC60DDAM45T1G	
		24	70	SP3F	Yes	APTC60DDAM24T3G	APTC60DSKM24T3G
800		150	21	SP3F	Yes	APTC80DDA15T3G	
1000	MOS 7	350	17	SP3F	Yes		APTM100DSK35T3G

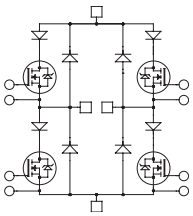
Full Bridge

V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
100	FREDFET 5	4.5	207	SP6C	No	APTM10HM05FG
		19	50	SP3F	Yes	APTM10HM19FT3G
		9	100	SP3F	Yes	APTM10HM09FT3G
200	FREDFET 7	20	62	SP4	Yes	APTM20HM20FTG
		16	74	SP4	Yes	APTM20HM16FTG
		10	125	SP6C	No	APTM20HM10FG
		8	147	SP6C	No	APTM20HM08FG
500	FREDFET 7	140	18	SP3F	Yes	APTM50H14FT3G
		100	24	SP3F	Yes	APTM50H10FT3G
		75	32	SP4	Yes	APTM50HM75FTG
		75	32	SP3F	Yes	APTM50HM75FT3G
		65	37	SP4	Yes	APTM50HM65FTG
		65	37	SP3F	Yes	APTM50HM65FT3G
		38	64	SP6C	No	APTM50HM38FG
		35	70	SP6C	No	APTM50HM35FG
	FREDFET 8	150	19	SP1F	Yes	APTM50H15FT1G
600	Superjunction MOSFET	45	38	SP1F	Yes	APTC60HM45T1G
		24	70	SP3F	Yes	APTC60HM24T3G
	FREDFET 8	230	15	SP1F	Yes	APTM60H23FT1G
800	Superjunction MOSFET	150	21	SP1F	Yes	APTC80H15T1G
		290	11	SP3F	Yes	APTC80H29T3G
		150	21	SP3F	Yes	APTC80H15T3G
1000	FREDFET 7	450	14	SP3F	Yes	APTM100H45FT3G
		350	17	SP4	Yes	APTM100H35FTG
		350	17	SP3F	Yes	APTM100H35FT3G
		180	33	SP6C	No	APTM100H18FG
	FREDFET 8	460	14	SP3F	Yes	APTM100H46FT3G
1200	FREDFET 7	290	25	SP6C	No	APTM120H29FG
	FREDFET 8	1400	6	SP1F	Yes	APTM120H140FT1G



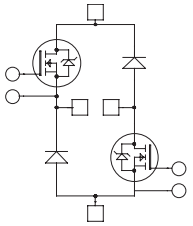
Full Bridge + Series and Parallel

V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
200	MOS 7™	20	62	SP4	Yes	APTM20HM20STG
500	MOS 7	75	32	SP4	Yes	APTM50HM75STG
1000	MOS 7	450	13	SP4	Yes	APTM100H45STG



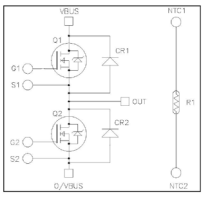
Asymmetrical Bridge

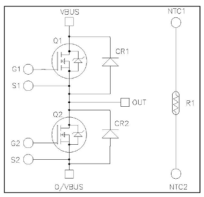
V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
100	MOS 5	4.5	207	SP6C	No	APTM10DHM05G
500	MOS 7	38	64	SP6C	No	APTM50DHM38G
600	Superjunction MOSFET	24	70	SP3F	Yes	APTC60DHM24T3G

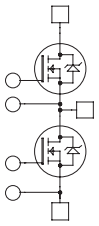


Phase Leg

V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
100	FREDFET 5	4.5	207	SP4	Yes	APTM10AM05FTG
		2.25	370	SP6C	Option	APTM10AM02FG
200	FREDFET 7	10	125	SP4	Yes	APTM20AM10FTG
		8	147	SP4	Yes	APTM20AM08FTG
		5	250	SP6C	Option	APTM20AM05FG
		5	280	LP8		MSCM20AM058G
		4	300	SP6C	Option	APTM20AM04FG
500	FREDFET 7	38	64	SP4	Yes	APTM50AM38FTG
		35	70	SP4	Yes	APTM50AM35FTG
		19	125	SP6C	Option	APTM50AM19FG
		17	140	SP6C	Option	APTM50AM17FG
600	Superjunction MOSFET	45	38	SP1F	Yes	APTC60AM45T1G
		24	70	SP1F	Yes	APTC60AM24T1G
	FREDFET 8	110	30	SP1F	Yes	APTM60A11FT1G
1000	FREDFET 7	180	33	SP4	Yes	APTM100A18FTG
		90	59	SP6C	Option	APTM100AM90FG
1200	FREDFET 7	290	25	SP4	Yes	APTM120A29FTG
		150	45	SP6C	Option	APTM120A15FG

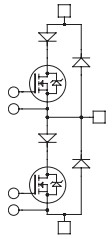






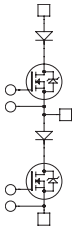
Phase Leg + Series and Parallel Diodes

V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
200	MOS 7™	10	125	SP4	Yes	APTM20AM10STG
		6	225	SP6C	No	APTM20AM06SG
500	MOS 7	38	64	SP4	Yes	APTM50AM38STG
		24	110	SP6C	No	APTM50AM24SG
1000	MOS 7	230	26	SP4	Yes	APTM100A23STG
		130	49	SP6C	No	APTM100A13SG
1200	MOS 7	200	37	SP6C	No	APTM120A20SG



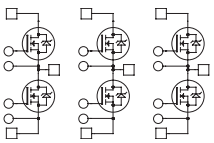
Phase Leg + Series Diodes

V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
1000	MOS 7	130	49	SP6C	No	APTM100A13DG
1200	MOS 7	200	37	SP6C	No	APTM120A20DG



Triple Phase Leg

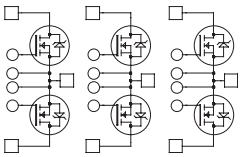
V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
75	MOSFET	4.2	90	SP6P	Option	APTM08TAM04PG
100	FREDFET 5	19	50	SP6P	Option	APTM10TAM19FPG
		9	100	SP6P	Option	APTM10TAM09FPG
200	FREDFET 7	16	74	SP6P	Option	APTM20TAM16FPG
500	FREDFET 7	65	37	SP6P	Option	APTM50TAM65FPG
600	Superjunction MOSFET	24	70	SP6P	Yes	APTC60TAM24TPG
1000	FREDFET 7	350	17	SP6P	Option	APTM100TA35FPG



Three-phase Bridge

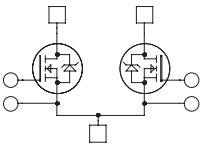
V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
200	FREDFET 5	16	77	SP4		MSCM20XM16F4G
	FREDFET 5	10	84	SP3X		MSCM20XM10T3XG

Triple Dual Common Source



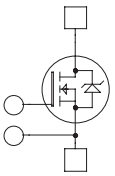
V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
800	Superjunction MOSFET	150	21	SP6P	Option	APTC80TDU15PG

Dual Common Source



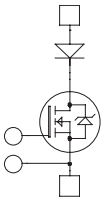
V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
100	MOS 5	2.25	370	SP6C	No	APTM10DUM02G
200	MOS 7™	8	147	SP4	Yes	APTM20DUM08TG
		5	250	SP6C	No	APTM20DUM05G
		4	300	SP6C	No	APTM20DUM04G
1200	MOS 7	150	45	SP6C	No	APTM120DU15G

Single Switch



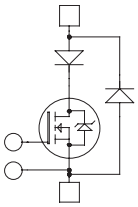
V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
100	FREDFET 5	2.25	430	SP6C	Option	APTM10UM02FAG
		1.5	640	SP6C	Option	APTM10UM01FAG
200	FREDFET 7	3	434	SP6C	Option	APTM20UM03FAG
500	FREDFET 7	9	371	SP6C	Option	APTM50UM09FAG
1000	FREDFET 7	60	97	SP6C	Option	APTM100UM60FAG
		45	160	SP6C	Option	APTM100UM45FAG
1200	FREDFET 7	70	126	SP6C	Option	APTM120UM70FAG

Single Switch + Series Diode



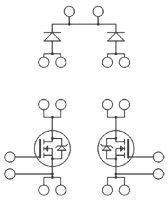
V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
1000	MOS 7	65	110	SP6C	No	APTM100UM65DAG
		45	160	SP6C	No	APTM100UM45DAG
1200	MOS 7	70	126	SP6C	No	APTM120UM70DAG

Single Switch + Series and Parallel Diodes



V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
200	MOS 7	4	310	SP6C	Option	APTM20UM04SAG
500	MOS 7	13	250	SP6C	Option	APTM50UM13SAG
1000	MOS 7	65	110	SP6C	Option	APTM100UM65SAG
1200	MOS 7	100	86	SP6C	Option	APTM120U10SAG

Interleaved PFC

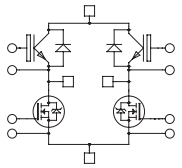


V_{DSS} (V)	MOSFET Type	$R_{DS(on)}$ (mΩ)	I_D (A) T_C = 80°C	Package	NTC	Part Number
600	Superjunction MOSFET	45	38	SP1F	Yes	APTC60VDAM45T1G
		24	70	SP3F	Yes	APTC60VDAM24T3G

Renewable Energy Power Module

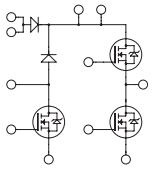
Full Bridge

V_{CES} (V)	Technology	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
600	Mix Trench IGBT & Superjunction MOSFET	50	83 mΩ/1.5	SP1F	Yes	APTCV40H60CT1G
		50	45 mΩ/1.5	SP3F	Yes	APTCV50H60T3G



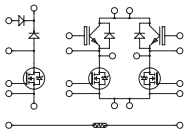
PFC + Bypass Diode + Phase Leg

V_{CES} (V)	Technology	I_D (A) T_C = 80°C	$R_{DS(on)}$ (mΩ) at Rated I_D	Package	NTC	Special	Part Number
600	Superjunction MOSFET	38	45	SP1F	N/A	10A PFC mSiC Diode	APTC60AM45BC1G
		38	45	SP1F	N/A		APTC60AM45B1G



PFC + Bypass Diode + Full Bridge

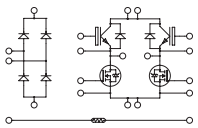
V_{CES} (V)	Technology	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Special	Part Number
600	Mix Trench IGBT & Superjunction MOSFET	38	45 mΩ/1.5	SP3F	Yes	20A PFC mSiC Diode	APTCV60HM45BC20T3G
		38	45 mΩ/1.5	SP3F	Yes		APTCV60HM45BT3G



Secondary Fast Rectifier + Full Bridge

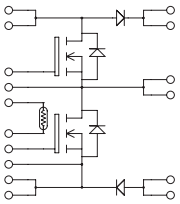
V_{CES} (V)	Technology	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Special	Part Number
600	Mix Trench IGBT & Superjunction MOSFET	38	45 mΩ/1.5	SP3F	Yes	20A SiC Antiparallel Diode	APTCV60HM45RCT3G
		38	45 mΩ/1.5	SP3F	Yes		APTCV60HM45RT3G
	Trench 3	50	1.5	SP3F	Yes		APTGT50H60RT3G

$R_{DS(on)}$ value for the MOSFETs in mΩ and $V_{CE(on)}$ value for the IGBTs in Volts



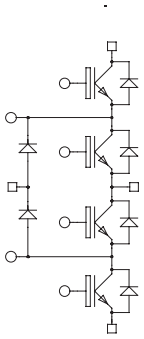
Boost Buck

V_{CES} (V)	Technology	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
600	Superjunction MOSFET	70	24 mΩ	SP3F	Yes	APTC60BBM24T3G
	Trench 3	100	1.5	SP3F	Yes	APTGT100BB60T3G

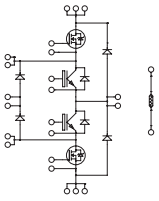


Three-level NPC Inverter

V_{CES} (V)	Technology	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Part Number
600	Trench 3	20	1.5	SP1F	No	APTGT20TL601G
		30	1.5	SP1F	No	APTGT30TL601G
		50	1.5	SP3F	Yes	APTGT50TL60T3G
		50	1.5	SP1F	No	APTGT50TL601G
		75	1.5	SP3F	Yes	APTGT75TL60T3G
		100	1.5	SP3F	Yes	APTGT100TL60T3G
		150	1.5	SP6C	No	APTGT150TL60G
		200	1.5	SP6C	No	APTGT200TL60G
		300	1.5	SP6C	No	APTGT300TL60G
650	Trench 3	300	1.5	SP6C	No	APTGT300TL65G
		400	1.5	SP6C	No	APTGT400TL65G
	Trench 4 Fast	50	1.85	SP3F	Yes	APTGLQ50TL65T3G
1200	Trench 4	60	1.85	SP3F	Yes	APTGL60TL120T3G
		240	1.8	SP6C	No	APTGL240TL120G
1700	Trench 3	100	2	SP6C	No	APTGT100TL170G

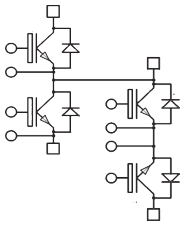


V_{CES} (V)	Technology	$R_{DS(on)}$ Superjunction MOSFET (mΩ)	$V_{CE\ (ON)}$ IGBT (V)/I_C (A)	Package	NTC	Part Number
600	Mix Trench IGBT and Superjunction MOSFET	24	1.5/75	SP3F	Yes	APTCV60TLM24T3G
		45	1.5/75	SP3F	Yes	APTCV60TLM45T3G
		99	1.5/30	SP3F	Yes	APTCV60TLM99T3G



T-Type 3-Level Inverter

V_{CES} (V)	Technology	I_C (A) T_C = 80°C	$V_{CE\ (ON)}$ (V) at Rated I_C	Package	NTC	Special	Part Number
600/1200	Trench 4 Fast	40	2.05	SP3F	Yes	10A/600V mSiC Diode	APTGLQ40HR120CT3G
		80	2.05	SP3F	Yes	30A/600V mSiC Diode	APTGLQ80HR120CT3G
		200	2.05	SP6C	No		APTGLQ200HR120G



Vienna Rectifier

V_{CES} (V)	IGBT Type	I_C (A) TC = 80°C	$V_{CE(ON)}$ (V) at Rated Ic	Package	NTC	Part Number
		40	45 mΩ	SP6P	YES	MSCC60VRM45TAPG
		81	23 mΩ	SP4		MSCC60AM23C4AG
650	Trench 5	80	1.65	SP1F		MSCGTQ100HD65C1AG

$R_{DS(on)}$ value for the MOSFETs in mΩ and $V_{CE(on)}$ value for the IGBTs in Volts

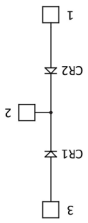
mSiC Diode Modules

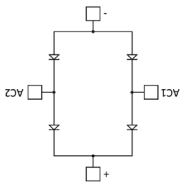
Power Module Advantages

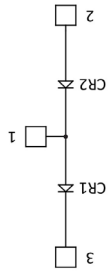
- High-speed switching
- Low switching losses
- Low-input capacitance
- High-power density
- Low-profile packages
- Minimum parasitic inductance
- Lower system cost
- Standard and custom modules
- 30+ years design experience

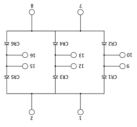
mSiC Diode Modules

Part Number	Configuration	Voltage (V)	Current (A)	VF (V)	Package
MSCDC100KK70D1PAG	Dual Common Cathode	700	100	1.5	D1P
MSCDC150KK70D1PAG			150	1.5	D1P
MSCDC200KK70D1PAG			200	1.5	D1P
MSCDC100KK120D1PAG		1200	100	1.5	D1P
MSCDC150KK120D1PAG			150	1.5	D1P
MSCDC200KK120D1PAG			200	1.5	D1P
MSCDC100KK170D1PAG		1700	100	1.5	D1P
MSCDC150KK170D1PAG			150	1.5	D1P
MSCDC200KK170D1PAG			200	1.5	D1P
MSC50DC70HJ	Full Bridge	700	50	1.5	SOT-227
MSCDC50H701AG				1.5	SP1F
MSCDC100H70AG			100	1.5	SP6C
MSCDC200H70AG			200	1.5	SP6C
MSC50DC120HJ		1200	50	1.5	SOT-227
MSCDC50H1201AG				1.5	SP1F
MSCDC100H120AG			100	1.5	SP6C
MSCDC200H120AG			200	1.5	SP6C
MSC50DC170HJ		1700	50	1.5	SOT-227
MSCDC50H1701AG				1.5	SP1F
MSCDC100H170AG			100	1.5	SP6C
MSCDC200H170AG			200	1.5	SP6C
MSCDC100A70D1PAG	Phase Leg	700	100	1.5	D1P
MSCDC150A70D1PAG			150	1.5	D1P
MSCDC200A70D1PAG			200	1.5	D1P
MSCDC300A70AG			300	1.5	SP6C
MSCDC450A70AG			450	1.5	SP6C
MSCDC600A70AG			600	1.5	SP6C
MSCDC100A120D1PAG		1200	100	1.5	D1P
MSCDC150A120D1PAG			150	1.5	D1P
MSCDC200A120D1PAG			200	1.5	D1P
MSCDC300A120AG			300	1.5	SP6C
MSCDC450A120AG			450	1.5	SP6C
MSCDC600A120AG			600	1.5	SP6C
MSCDC100A170D1PAG		1700	100	1.5	D1P
MSCDC150A170D1PAG			150	1.5	D1P
MSCDC200A170D1PAG			200	1.5	D1P
MSCDC300A170AG			300	1.5	SP6C
MSCDC450A170AG			450	1.5	SP6C
MSCDC600A170AG			600	1.5	SP6C
MSCDC50X701AG	Three-phase Bridge	700	50	1.5	SP1F
MSCDC50X1201AG		1200	50	1.5	SP1F
MSCDC50X1701AG		1700	50	1.5	SP1F

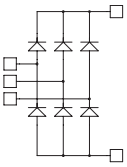


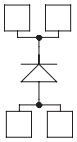






Diode Power Modules



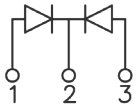


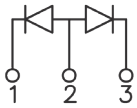
V_{RRM} (V)	Diode Type	I_F (A) T_C = 80°C	V_F (V) T_C = 80°C	Package	Part Number
200	FRED	500	1.1	LP4	APTDF500U20G
400		500	1.5		APTDF500U40G
600		450	1.8		APTDF450U60G
1000		430	2.3		APTDF430U100G
1200		400	2.5		APTDF400U120G

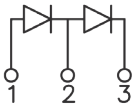
Single Diode

V_{RRM} (V)	Diode Type	I_F (A) T_C = 80°C	V_F (V) T_J = 25°C	Package	Part Number
1600	Rectifier	40	1.3	SP1F	APTDR40X1601G
		90	1.3	SP1F	APTDR90X1601G

Common Cathode–
Common Anode–Doubler



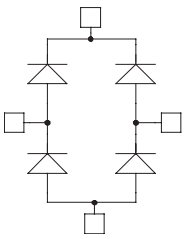




V_{RRM} (V)	Diode Type	I_F (A) per Diode	V_F (V) T_J = 25°C	Package	Common Cathode	Common Anode	Doubler
200	FRED	400	1	SP6C	APTDF400KK20G	APTDF400AA20G	APTDF400AK20G
600			1.6		APTDF400KK60G	APTDF400AA60G	APTDF400AK60G
1000			2.1		APTDF400KK100G	APTDF400AA100G	APTDF400AK100G
1200			2.4		APTDF400KK120G	APTDF400AA120G	APTDF400AK120G
1700			2.2		APTDF400KK170G	APTDF400AA170G	APTDF400AK170G

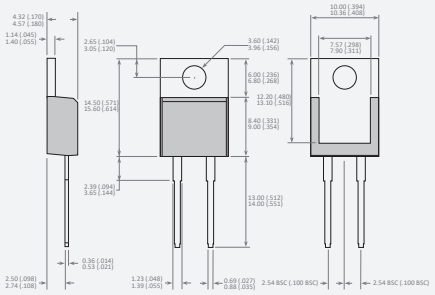
Full Bridge

V_{RRM} (V)	Diode Type	I_F (A) T_C = 80°C	V_F (V) T_C = 80°C	Package	Part Number
200	FRED	30	1	SOT-227	APT30DF20HJ
		60	1	SOT-227	APT60DF20HJ
		100	1	SP4	APTDF100H20G
600		30	1.8	SP1F	APTDF30H601G
		30	1.8	SOT-227	APT30DF60HJ
		60	1.8	SOT-227	APT60DF60HJ
		60	1.8	SP1F	APTDF60H601G
		100	1.6	SOT-227	APT100DL60HJ
		100	1.6	SP1F	APTDF100H601G
		200	1.6	SP6C	APTDF200H60G
1000		30	2.1	SOT-227	APT30DF100HJ
		100	2.1	SP4	APTDF100H100G
		200	2.1	SP6C	APTDF200H100G
1200		30	2.6	SP1F	APTDF30H1201G
		60	2.6	SP1F	APTDF60H1201G
		75	1.6	SOT-227	APT75DL120HJ
		200	2.4	SP6C	APTDF200H120G
1700		50	1.8	SOT-227	APT50DF170HJ
		75	1.8	SOT-227	APT75DF170HJ
1600	RECTIFIER	40	1.3	SOT-227	APT40DR160HJ
		90	1.3	SOT-227	APT90DR160HJ



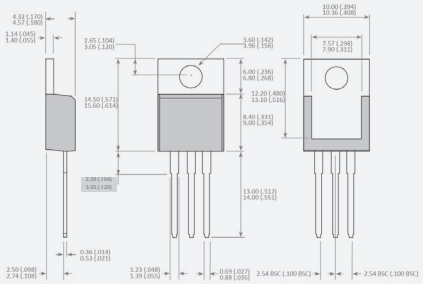
Power Discrete and Module Outlines

TO-220 2-Lead



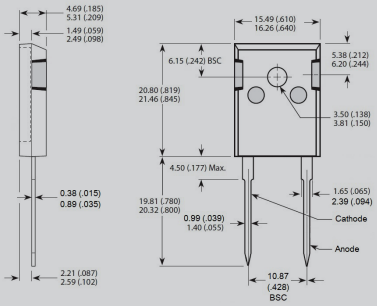
Dimensions in Millimeters and (Inches)

TO-220 3-Lead



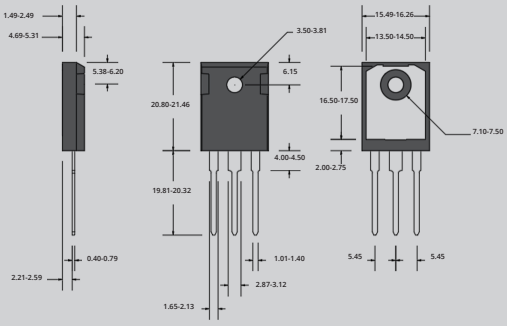
Dimensions in Millimeters and (Inches)

TO-247 2-Lead



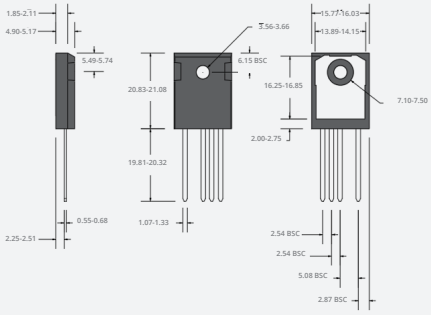
Dimensions in Millimeters and (Inches)

TO-247 3-Lead



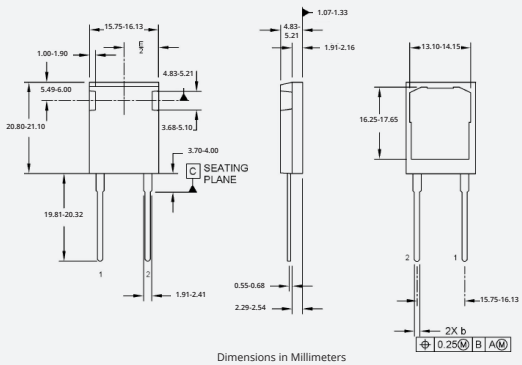
Dimensions in Millimeters

TO-247 4-Lead



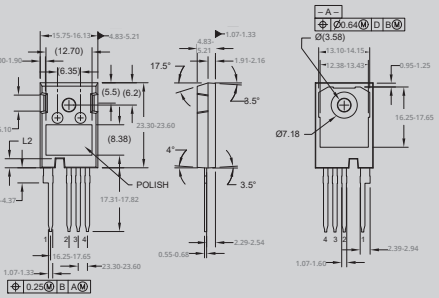
Dimensions in Millimeters

T-MAX®



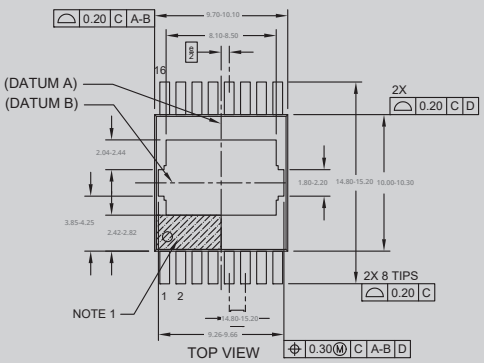
Dimensions in Millimeters

TO-247-4L Notch



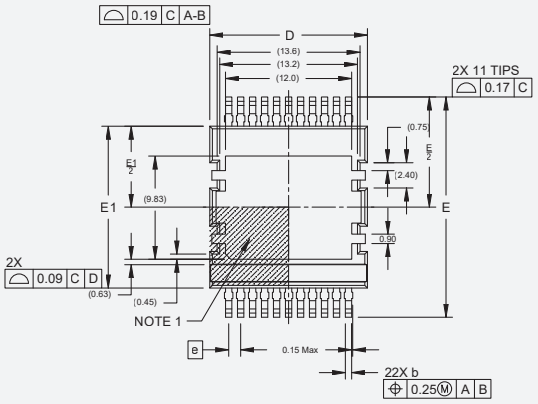
Dimensions in Millimeters

PSMT

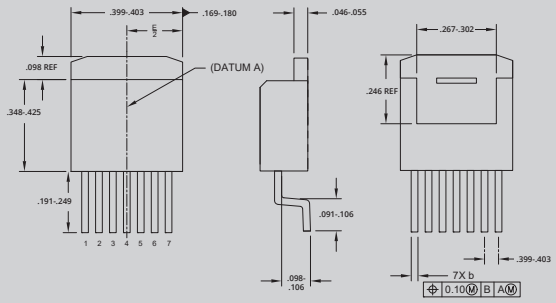


Dimensions in Millimeters

QDPAK [Q]

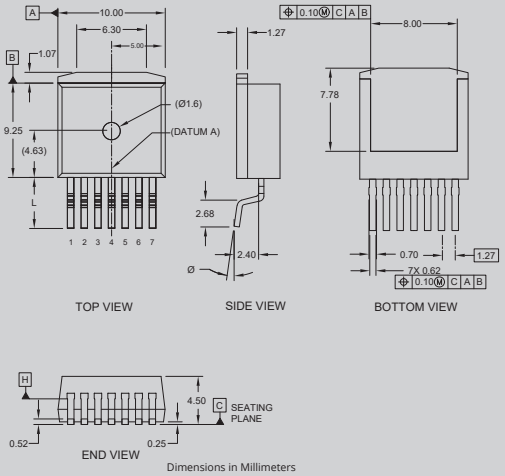


TO-263-7
(D2PAK-7)



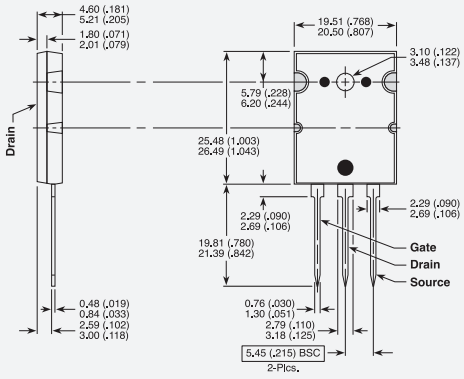
Dimensions in Inches

TO-263-7 XL
(D2PAK-7L XL)



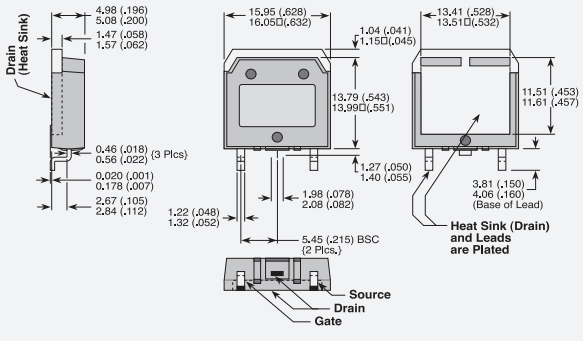
Dimensions in Millimeters

TO-264



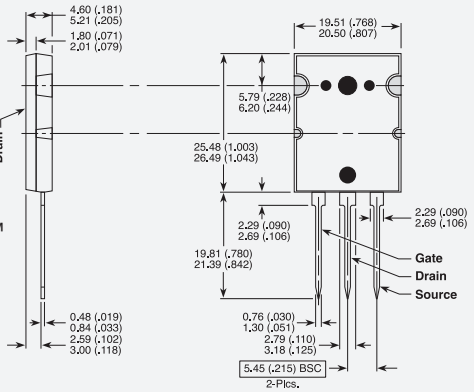
Dimensions in Millimeters and (Inches)

TO-268
(D3PAK)



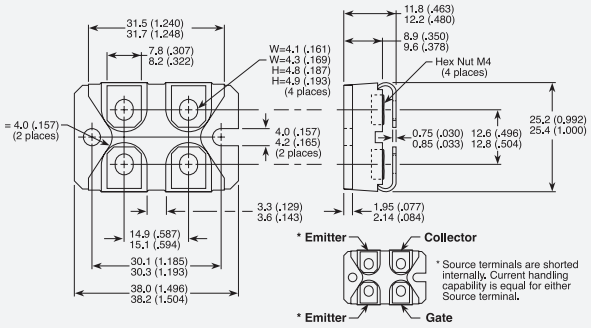
Dimensions in Millimeters and (Inches)

TO-264 MAX™

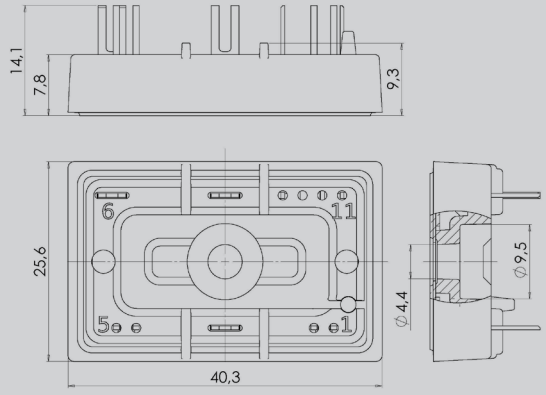


These dimensions are equal to the TO-264 without the mounting hole.

SOT-227

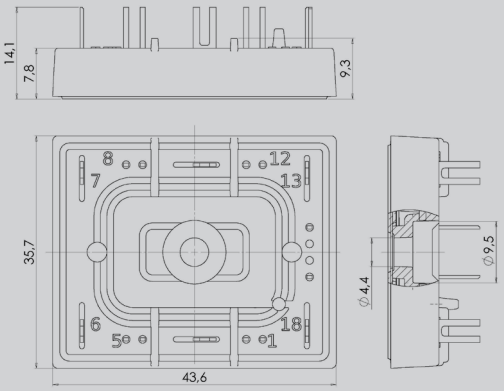


BL1

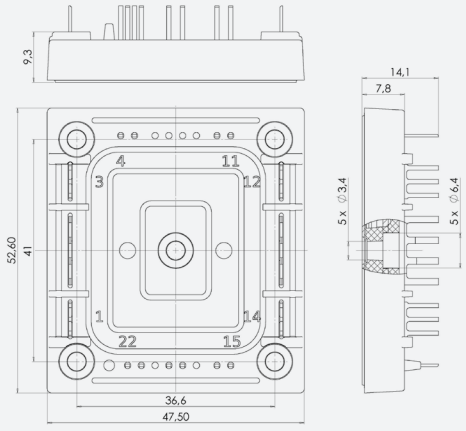


Dimensions in Millimeters

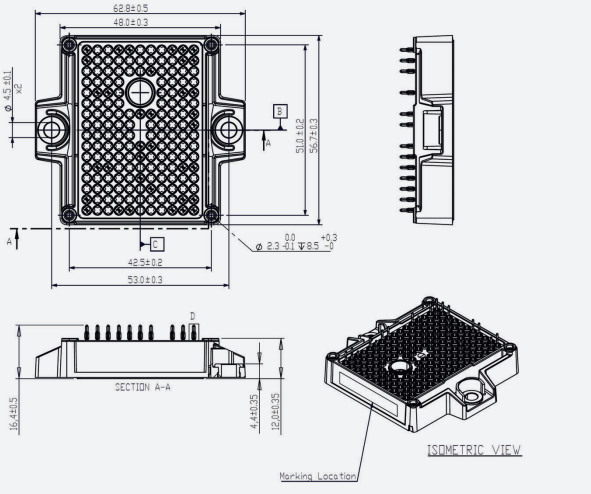
BL2



BL3

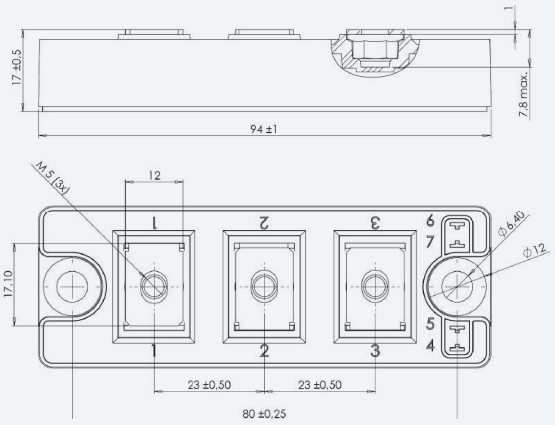


BZ2

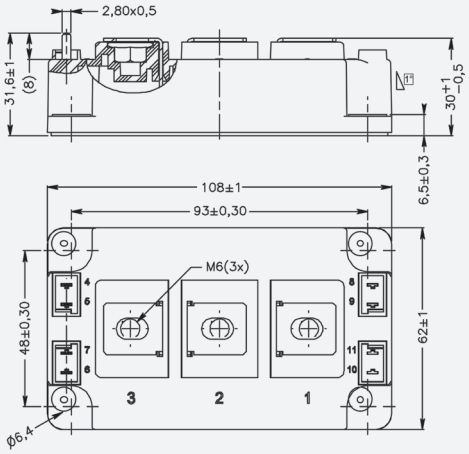


Pinout location depends on the module configuration. Please refer to the product datasheet for pin assignments. All dimensions in millimeters unless otherwise indicated.

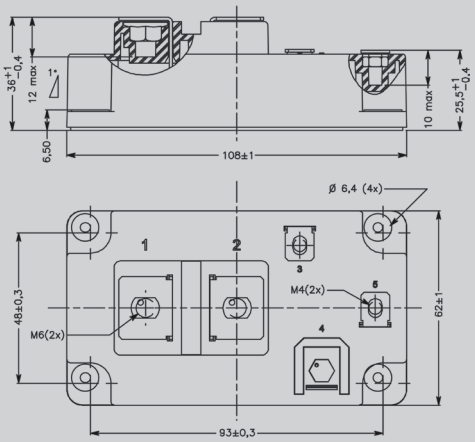
D1P



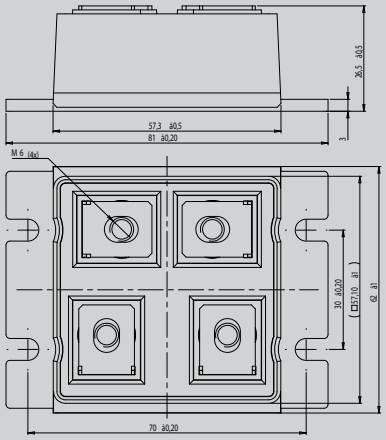
D3



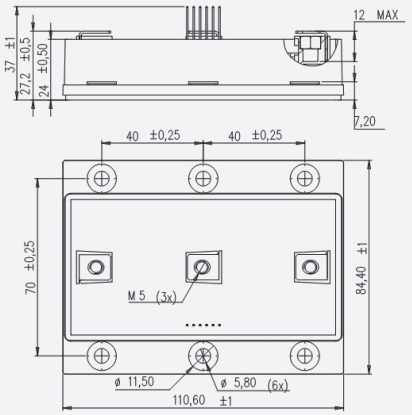
D4



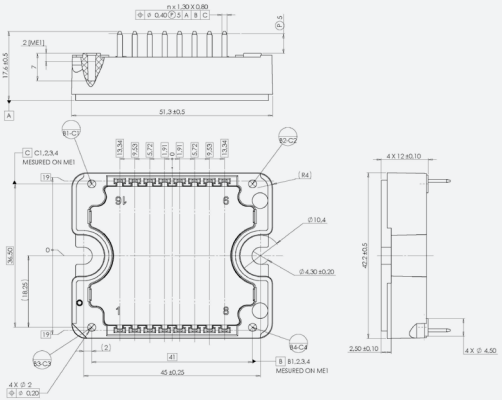
LP4



LP8

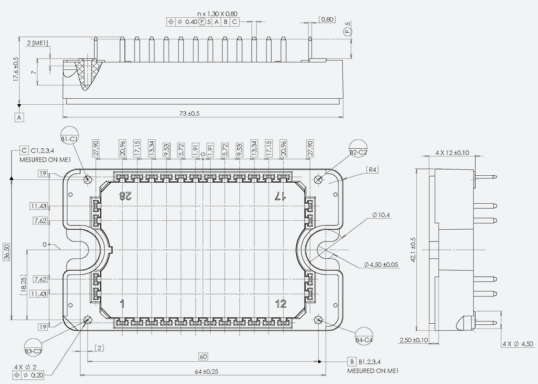


SP1F

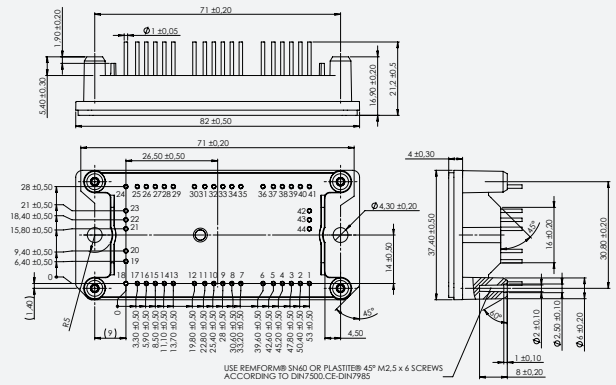


Pinout location depends on the module configuration. Please refer to the product datasheet for pin assignments. All dimensions in millimeters.

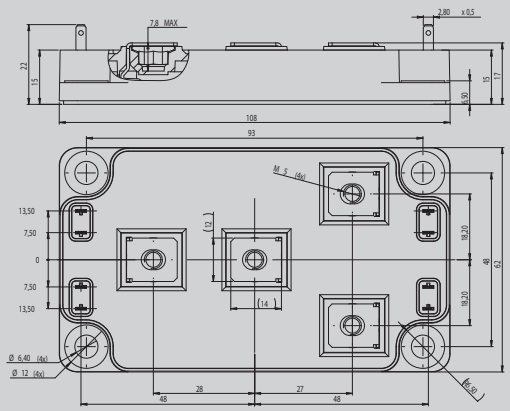
SP3F



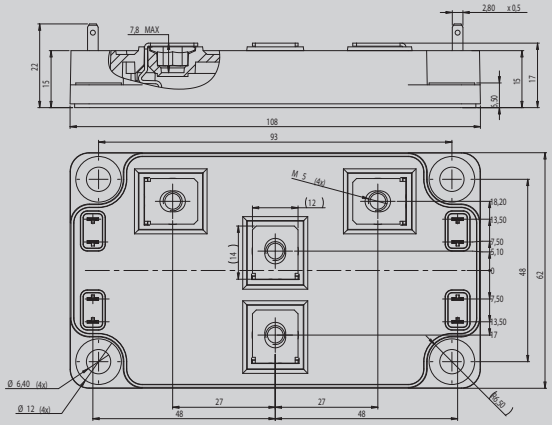
SP3X



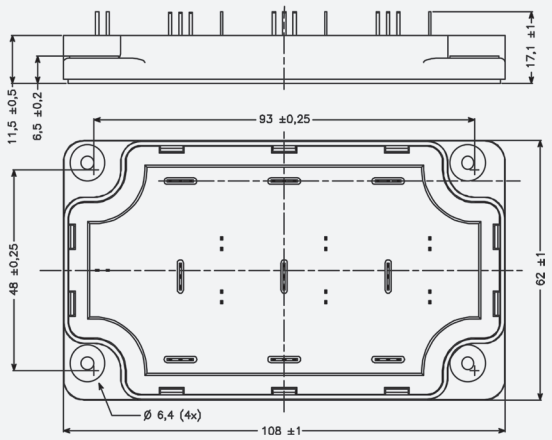
SP6C Four Outputs, Version 1



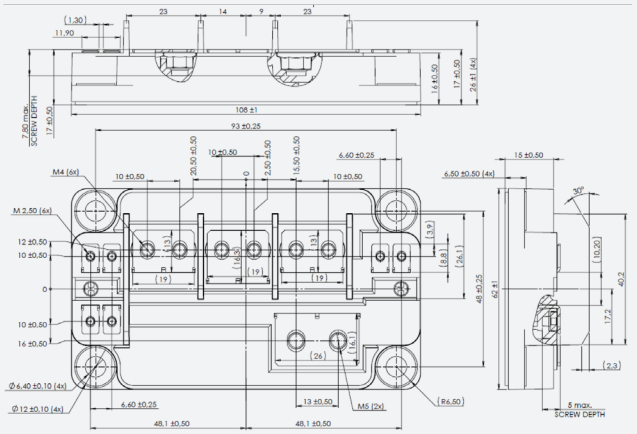
SP6C Four Outputs, Version 2



SP6P

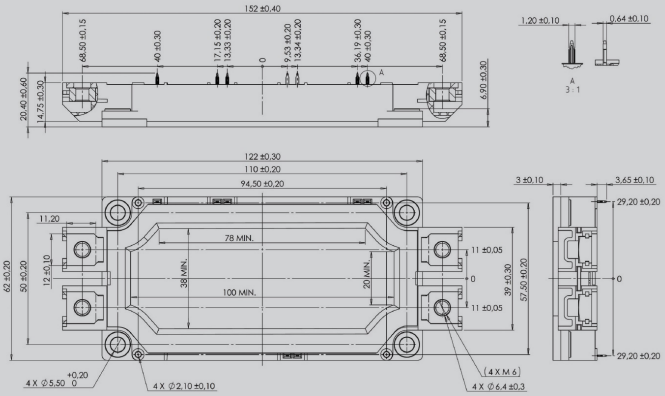


SP6LI

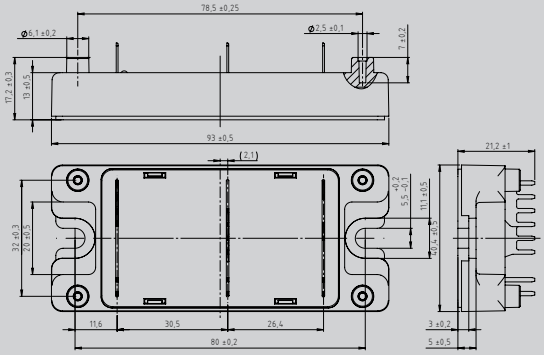


Pinout location depends on the module configuration. Please refer to the product datasheet for pin assignments. All dimensions in millimeters.

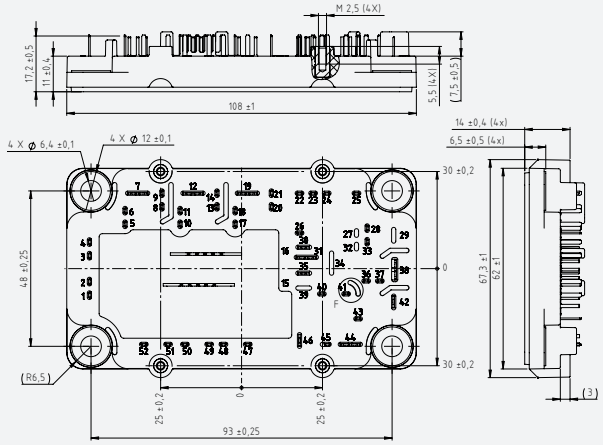
DP3



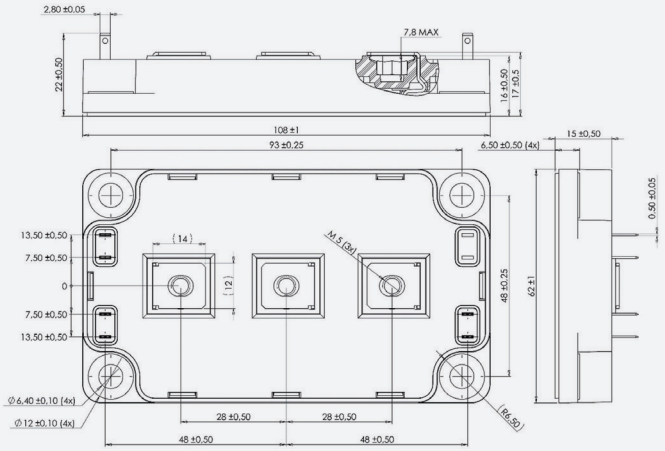
SP4



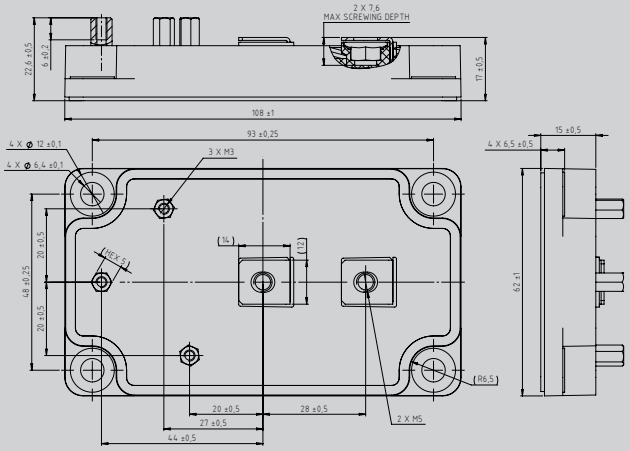
SP6HPD



SP6C Three Outputs



SP6C Resin



Pinout location depends on the module configuration. Please refer to the product datasheet for pin assignments. All dimensions in millimeters.

High-Voltage Reference Designs

SiC Hardware Design Resources

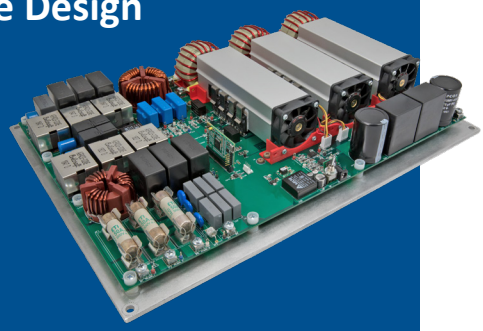
Unlock the full potential of your power systems with our cutting-edge mSiC® solutions. Our comprehensive suite of SiC reference designs, technology demonstrators and evaluation kits are engineered to streamline your development process, enhance performance and slash your time-to-market. Dive into high-efficiency power conversion with our state-of-the-art tools tailored to empower engineers and innovators in harnessing the exceptional thermal and electrical properties of SiC. Whether you're designing for automotive, industrial or energy applications, our hardware resources are your gateway to a future of unparalleled power management.

SiC Design Support - Hardware

Hardware Platform	AC-DC	DC-DC	DC-AC	SSCB	Evaluation Board
High-Voltage Auxiliary E-Fuse Reference Design				✓	
High-Voltage Bidirectional Auxiliary E-Fuse Reference Design				✓	
High-Voltage Hardware-Based E-Fuse Reference Design				✓	
3.8 kW/7.6 kW Totem Pole Demonstration Application	✓		✓		
30 kW 3-Phase Vienna PFC Reference Design	✓				
11 kW Dual Active Bridge DC-DC Demonstration Application		✓			
11 kW Totem-Pole Demonstration Application	✓		✓		
250-1000V (63W) Auxiliary Power Supply Reference Design		✓			
150 kVA 3-Phase SiC Power Stack Reference Design	✓	✓	✓		
1.5 kW E-2W EV Charger Reference Design	✓		✓		
45W Auxiliary Power Supply for 800V Traction Inverters Reference Design		✓			
SP6LIEVB					✓
PSMT Half-Bridge Reference Design			✓		
3kW Single-Phase Grid-Tied Inverter Reference Design			✓		
4 kW DC-DC Demonstration Application		✓			
45W Auxiliary Power Supply for 800V Traction Inverters	✓	✓	✓		
Isolated Bias Generator for SiC Gate Drivers Reference Design					
Single-Channel Discrete Gate Driver Evaluation Board					✓
Single-Channel Module Gate Driver Evaluation Board					✓
Half Bridge Evaluation Board					✓
Power Motherboard Fast Evaluation Tool					✓

Vienna 3-Phase Power Factor Correction (PFC) Reference Design

The 3-phase Vienna PFC reference design for Hybrid Electric Vehicle (HEV) and Electric Vehicle (EV) chargers and high-power switch mode power supply applications achieves 98.6% efficiency at 30 kW output power.

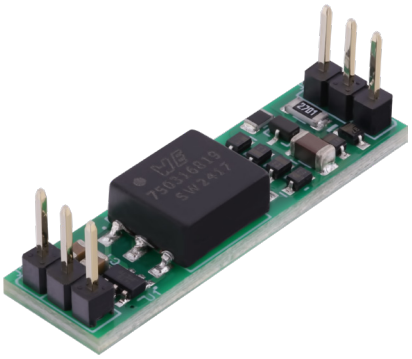


microchip.com/pfc

- High-Efficiency 30 kW Operation: Optimized for high-power PFC applications
- Updated to dsPIC33AK Digital Signal Controller
- Improved software architecture with modular structure, integrated diagnostics and enhanced code documentation
- Optimized PCB layout designed for enhanced safety, current stress management, mechanical robustness, and noise immunity
- Advanced SiC Power Devices:
  - 700V mSiC® MOSFETs with high avalanche and repetitive UIS capability
  - 1200V mSiC Schottky Barrier Diodes
- Versatile Input Voltage: Supports 3-phase 380/400V RMS input at 50 Hz or 60 Hz
- High-Frequency Switching: Operates at 140 kHz switching frequency
- Robust DC Output: Delivers a stable 700V DC output voltage
- CAN FD communication support, including GUI and data logger functionality for monitoring, diagnostics and system evaluation
- Programmable soft-start and controlled system bring-up, with PFC enabled only after all operational requirements are verified
- Automatic system shutdown in response to fault conditions or AC line dropout events
- Enhanced over-current protection featuring a 7.1 µs response time and a robust two-sample trip mechanism

Isolated Bias Generator for SiC Gate Drivers Reference Design

The Isolated Bias Generator for SiC Gate Drivers Reference Design is based on the MCP14T0517 push-pull transformer driver. The board provides galvanic isolated and regulated bias voltage of +20V with respect to 0V and -5V with respect to 0V at up to 100 mA of current. The board features configurable ENABLE pin for external control and synchronization. MCP14T0517A/B drivers designed for small form factor isolated power supply applications with a switching frequency of 150 kHz (MCP14T0517A) and 450 kHz (MCP14T0517B). The MCP14T0517A/B allows synchronization with multiple devices and operation at higher frequencies by applying an external clock of up to 1000 kHz.



https://www.microchip.com/en-us/tools-resources/reference-designs/isolated-bias-generator-for-sic-gate-drivers-reference-design

- Galvanically isolated bias power supply optimized for SiC gate driver applications
- Regulated +20V and –5V outputs referenced to a common return
- Supports up to 100 mA output current for reliable gate drive biasing
- Operates from a 5 V input supply with external enable control
- High switching frequency operation enabling compact magnetics and reduced board area
- Integrated protection features including overcurrent and overtemperature protection
- Compact PCB footprint suitable for dense power stage layouts

3.8 kW/7.6 kW Totem Pole Demonstration Application

Featuring dsPIC® Digital Signal Controllers (DSCs) and silicon carbide (SiC) MOSFETs, this demonstration platform is part of an On-Board Charger (OBC) used for charging Electric Vehicles (EVs). This reference design also includes an 8-bit MCU, gate drivers, a buck regulator, a Switch-Mode Power Supply (SMPS) controller, push-pull PWM controller, CAN FD transceiver and LDO. The highly modular and configurable hardware with Plug-in-Modules (PIMs) and flexible software supports different modes of operation, including:



https://www.microchip.com/en-us/tools-resources/reference-designs/3-8kw-7-6kw-dspic33c-totem-pole-development-application

- Enables bidirectional power conversion for an Electric Vehicle (EV) On-Board Charger (OBC)
- Highly modular hardware and firmware that allows operation in different modes
- Supported by code generation tools to accelerate your development
- Forced-air cooled solution with AEC-Q100 qualified components

11 kW Dual Active Bridge DC-DC Demonstration Application

Featuring dsPIC Digital Signal Controllers (DSCs) and silicon carbide (SiC) MOSFETs, this demonstration platform is part of an On-Board Charger (OBC) used for charging Electric Vehicles (EVs). This system also includes an 8-bit MCU, gate drivers, a buck regulator, a Switch Mode Power Supply (SMPS) controller, push-pull PWM controller, CAN FD transceiver and LDO. The highly modular and configurable hardware with Plug-in-Modules (PIMs) and flexible software supports different modes of operation.

- 700–900 VDC input and output with bi-directional operation
- Non-linear/adaptive control algorithms for improved performance
- Forced-air cooled solution with AEC-Q100-qualified components

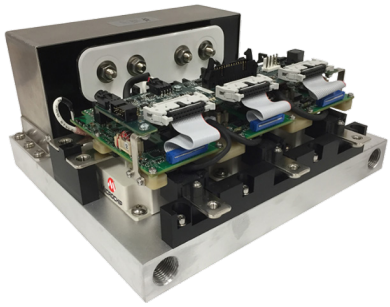


https://www.microchip.com/en-us/tools-resources/reference-designs/11-kw-dual-active-bridge-dc-dc-demonstration-application

Mersen 150 kVA 3-Phase SiC Power Stack Evaluation Kit

Designers of EVs, commercial transportation, renewable energy and energy storage systems can benefit from SiC stack solutions that drive performance and cost efficiencies and accelerate time to market.

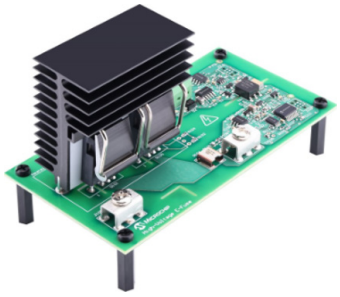
- 16 kW/L power density
- Up to 130°CTj
- 98% peak efficiency
- 1200V mSiC MOSFET Modules
- AgileSwitch® gate driver core
- 700 VDC/200 ARMS
- Compact water-cooled design
- Up to 20 kHz switching frequency



High-Voltage Auxiliary Electronic Fuse (E-Fuse) Demonstrator

You can use high-voltage auxiliary E-Fuse technology for HEV, EV and other non-automotive DC solid-state circuit breaker applications. This technology demonstrator leverages the benefits of our 700V and 1200V mSiC MOSFETs and other technologies to provide a complete solution.

- Configurable current limit profile
- LIN communication interface for configurability and diagnostics
- High-side or low-side drive configuration
- Short-circuit withstand time: 10 µs
- Rated current: 30A
- Low-voltage operating range: 9V to 16V
- High-voltage operating range: 200V to 900V
- Operating temperature range: −40°C to 85°C
- Automotive hardware design that uses only AEC-qualified components
- Six variants of this high-voltage auxiliary E-Fuse design that support 400V and 800V bus voltages and continuous current ratings of 10A, 20A and 30A
- Up to 20 kHz switching frequency

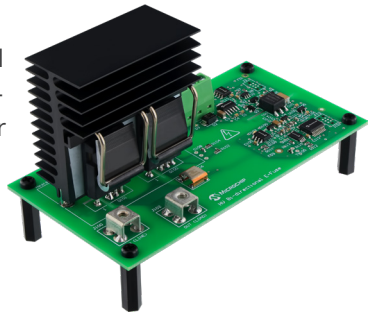


microchip.com/e-fuse

High-Voltage Bidirectional Auxiliary E-Fuse Reference Design

The High-Voltage Bidirectional Auxiliary E-Fuse reference design demonstrates a solid-state solution for protecting auxiliary high-voltage DC rails in automotive and industrial systems. The design provides bidirectional current interruption, enabling controlled isolation of faults regardless of current direction. It is intended as a functional replacement for conventional fuses, relays and contactors in auxiliary power paths where fast response, configurability and reset capability are required.

- For use in 400V and 800V DC systems
- Up to 15A continuous output load current
- Bidirectional auxiliary E-Fuse architecture
- 1200V SiC MOSFETs used by default (700V devices supported)
- Configurable time-current characteristic (TCC) curve
- Edge-triggered short-circuit detection
- Diagnostic monitoring of current, temperature, and bias supply
- LIN communication interface for configuration and diagnostics
- Flexible high-side or low-side system configuration

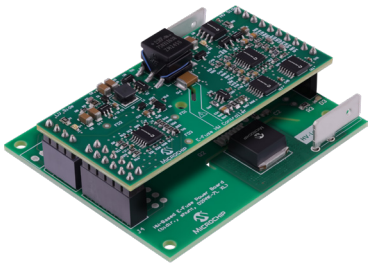


https://www.microchip.com/en-us/tools-resources/reference-designs/high-voltage-bidirectional-auxiliary-e-fuse-reference-design

High-Voltage Hardware-Based E-Fuse Reference Design

This fully hardware-based e-fuse reference design is optimized for high-voltage bidirectional applications, eliminating the need for an onboard microcontroller. Designed for both AC and DC systems, it supports 400V DC and 800V DC configurations and features bidirectional current blocking using mSiC MOSFETs. Advanced protection is built in, with configurable current trip profiles for rapid-fault response.

- Bidirectional current blocking with anti-series configuration
- Fast fault detection for high-voltage AC and DC systems
- Resettable design for simplified serviceability and packaging
- Modular control and power board architecture
- Scalable with multiple discrete component and package options

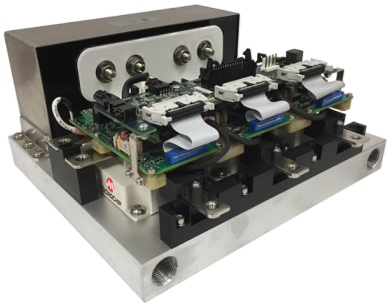


https://www.microchip.com/en-us/tools-resources/reference-designs/high-voltage-hardware-based-e-fuse-reference-design

Mersen 150 kVA 3-Phase SiC Power Stack Evaluation Kit

Designers of EVs, commercial transportation, renewable energy and energy storage systems can benefit from SiC stack solutions that drive performance and cost efficiencies and accelerate time to market.

- 16 kW/L power density
- Up to 130°CTj
- 98% peak efficiency
- 1200V mSiC MOSFET Modules
- AgileSwitch® gate driver core
- 700 VDC/200 ARMS
- Compact water-cooled design
- Up to 20 kHz switching frequency

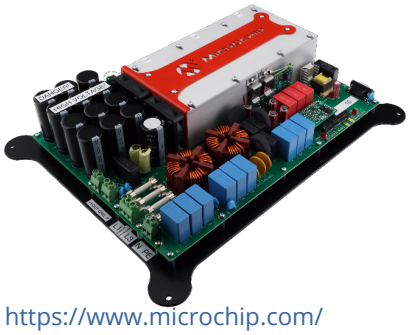


https://www.microchip.com/en-us/tools-resources/reference-designs/150-kva-3-phase-sic-power-stack-reference-design

11 kW Totem-Pole Demonstration Application

This demonstration platform features our mSiC MOSFETs, dsPIC® Digital Signal Controllers (DSCs). The demonstration platform also includes our 8-bit microcontroller, gate drivers, buck regulator, Switch Mode Power Supply (SMPS) controller, push-pull PWM controller, CAN FD transceiver and LDO. The highly modular and configurable hardware with Plug-in-Modules (PIMs) and flexible software support different modes of operation, including:

- Three-phase Power Factor Correction (PFC)
- One-phase PFC (single and multiple legs)
- Three-phase inverter
- One-phase inverter



https://www.microchip.com/en-us/tools-resources/reference-designs/11-kw-totem-pole-demonstration-application

3kW Single-Phase Grid-Tied Inverter Reference Design

This reference design delivers a robust and flexible solution for single-phase grid-tied solar applications, rated for a maximum power output of 3 kW.

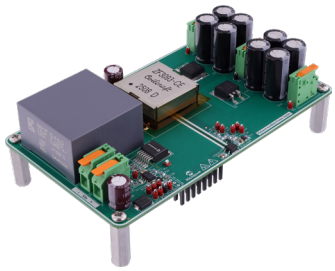
- Power and Performance – 3 kW single-phase output, up to 12 A, 95% peak efficiency, PF > 0.99, and <3% THD at full loads
- Wide Operating Range – PV input 80–450 V DC and AC mains range 180–260V AC
- Digital Control Flexibility – Fully digital Boost and DC-AC control with software-configurable grid current and voltage settings
- Advanced Protection – Anti-islanding, frequency monitoring, 2 kV surge protection and earth leakage



https://www.microchip.com/en-us/tools-resources/reference-designs/3-kw-single-phase-grid-tied-inverter-reference-design

45W Auxiliary Power Supply for 800V Traction Inverters Reference Design

Designed for the high voltage and reliability demands of EV, HEV, and PHEV traction inverters, this compact 45W auxiliary power supply features a high-voltage flyback converter with a wide 40V–1000V input range and dual outputs (+22V regulated, -6V unregulated). Optimized for 800V battery systems, it supports regenerative braking and ensures consistent performance. Using AEC-Q101 qualified 1400V mSiC MOSFETs, the design cuts switching losses and removes the need for a gate driver, boosting efficiency and reliability. An automotive-grade transformer provides reinforced isolation, while an active start-up circuit lowers standby power consumption.



microchip.com/auxps

- AEC-Q101 qualified 1400V mSiC MOSFETs reduce switching losses and eliminate the need for a gate driver, improving efficiency and thermal performance
- Supports 40V to 1000V input, making it adaptable for various EV architectures and scalable for higher power levels
- Automotive-grade transformer with reinforced isolation and active start-up ensures safety, reduces standby power and supports regenerative braking

https://www.microchip.com/en-us/tools-resources/reference-designs/45w-auxiliary-power-supply-for-800v-traction-inverters-reference-design

Two/Three-Wheeler EV Charger Reference Design with CAN Control

Our 1.5kW two/three-wheeler EV charger reference design is a digitally controlled front-end PFC + LLC converter, suitable for charging the 2/3wheeler battery from direct AC mains input with high power factor, low THD and high efficiency.



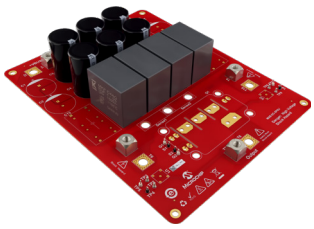
The reference design is mainly a combination of two PCBs, i.e.: Power Card and Control Card. The control card is vertically mounted on the power card using the 2.54 mm male-female connector and the current transformer (CT) is mounted on the control card. The current sensor wiring is done from the power card PCB and passing through the CT.

- 1.5 kW single-phase AC EV charger reference design with digitally controlled boost PFC + half-bridge LLC topology
- Input: 115–270 VAC; PFC DC bus: ~380–400 VDC; Output: up to 72V / 20A
- dsPIC33CK DSCs provide full digital control of PFC current shaping and LLC resonant conversion
- Power quality: PF > 0.99, low THD, sinusoidal input current
- Efficiency: up to ~94% with LLC ZVS operation and resonant tank design
- CAN / CAN-FD interface for charger control, telemetry, and diagnostics with vehicle ECU integration
- Real-time sensing of input/output voltage, current, temperature, and faults handled in firmware
- Two-board architecture (power card + control card) with isolation, EMI-compliant layout, and protection features for production-oriented designs

https://www.microchip.com/en-us/tools-resources/reference-designs/1-5kw-on-board-ev-charger-reference-design

SiC Evaluation Boards

SP6LI mSiC MOSFET Module Evaluation Board



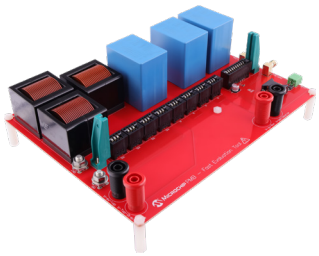
The SP6LI mSiC MOSFET module evaluation board is a versatile and essential tool for developers looking to leverage the SP6LI SiC module in power electronics. It streamlines the design process, reduces development risks and paves the way for the creation of energy-efficient, high-performance power electronic systems.

This system enables users to:

- Measure switching loss (Eon, Eoff and Qrr) and high-side and low-side overcurrent protection (DSAT)
- Optimize gate driver switching behavior
- Evaluate up to 1200V SP6LI mSiC MOSFET modules
- Perform extensive thermal testing to assess performance in practical situations

https://www.microchip.com/en-us/development-tool/MSCDR-SP6LIEVB-001

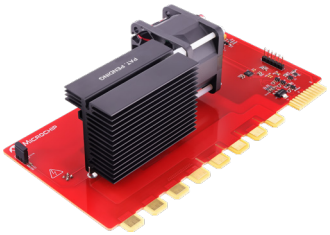
Power Motherboard Fast Evaluation Tool



- Operates as both a buck and boost converter for flexible evaluation of different power electronics configurations
- Supports Double Pulse Testing (DPT) for 700–1200V power devices, enabling precise measurement of switching loss and reverse recovery
- Delivers an operating voltage of up to 800V and a current capacity of up to 20A
- Minimizes development time to get to market quicker

https://www.microchip.com/en-us/development-tool/EV67D28A

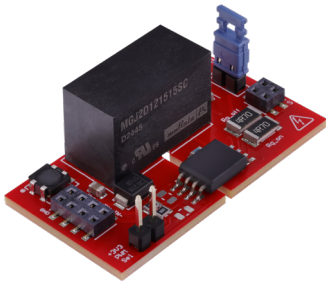
Half Bridge Board Evaluation Tool



- Support for up to 800V and 20A SiC MOSFETs for evaluation, enabling easy customization of gate drive parameters for precise performance tuning
- Interleaved bus connections minimize stray inductance, enhancing switching efficiency and reducing voltage overshoot for improved circuit stability
- PWM logic circuitry prevents inadvertent cross-conduction events, ensuring reliable operation

https://www.microchip.com/en-us/development-tool/EV40T43A

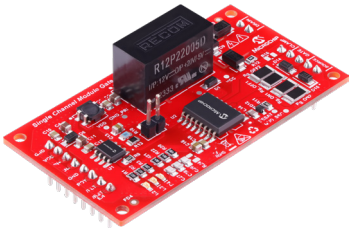
Single-Channel Discrete Gate Driver Evaluation Board



- The 2W isolated power supply enables driving MOSFETs at higher frequencies
- Designed to drive 700V and 1200V SiC MOSFETs with a 5A peak source and sink output current
- Separate gate turn-on and turn-off resistors allow you to optimize switching turn-on and turn-off slopes

https://www.microchip.com/en-us/development-tool/EV84K75A

Single-Channel Module Gate Driver Evaluation Board



- The 2W isolated power supply enables driving larger MOSFETs at higher frequencies
- Designed to drive 700V and 1200V SiC MOSFETs and modules, with a 10A peak source and sink output current
- Features desaturation protection circuitry, active Miller clamp and independent Under-Voltage Lockout (UVLO) to safeguard the system
- Separate gate turn-on and turn-off resistors allow you to optimize switching turn-on and turn-off slopes

https://www.microchip.com/en-us/development-tool/EV39N46A

Simulation and Models

Microchip offers a variety of simulation tools that help designers lower design complexities and shorten design cycle times. Both device and system level tools are available for use in device evaluation, system development and scaling of existing system level models.

Our models and simulation tools are built to save time and cost for development with SiC-based power systems. Our models help you achieve real-world accuracy to get your design to market faster. Our MPLAB SiC Power Simulator helps you evaluate mSiC products risk-free in multiple topologies using converter-level simulation models.



MPLAB® SiC Power Simulator

The MPLAB SiC Power Simulator calculates power losses and estimates junction temperature for SiC devices using lab testing data for common power converter topologies in DC-AC, AC-DC and DC-DC applications.

Relevant links: microchip.com/sicpowersim



MPLAB® Mindi™ Analog Simulator

Free SPICE circuit simulation tool that uses a SIMetrix/SIMPLIS simulation environment.

What's available: Free MPLAB Mindi Analog Simulator download. SiC Models are available for the 700V, 1200V and 1700V mSiC MOSFETs and Schottky Barrier Diodes

Relevant links: Simulation tool download at microchip.com/mplab/mplab-mindi and SiC models at microchip.com

SPICE Models

SPICE is a widely used circuit simulation framework that allows designers to evaluate device behavior within a complete circuit design. SPICE models enable this analysis and are commonly implemented across simulation environments, with added compatibility for tools such as Mindi, SIMetrix and LTspice to support a broader range of design workflows.

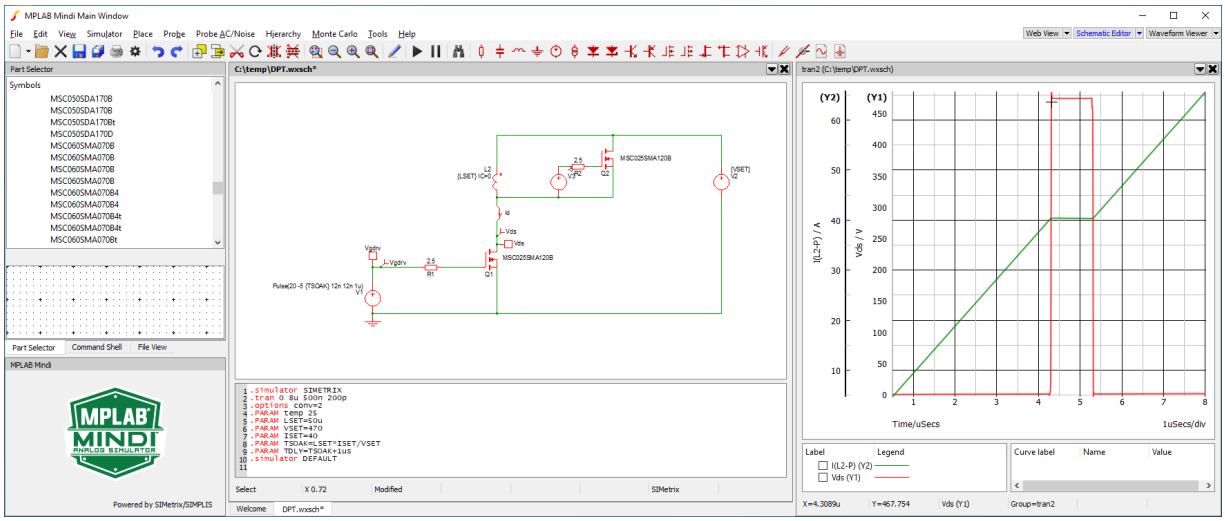
https://www.microchip.com/en-us/software-library/sic-products-spice-files

PLECS Models:

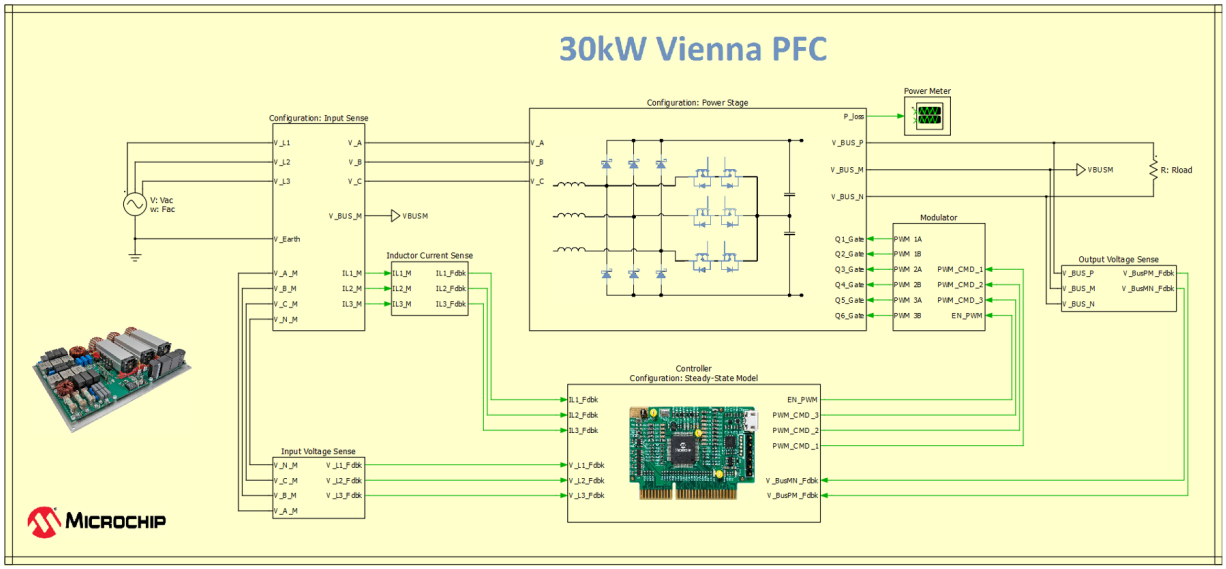
PLECS models enable accurate evaluation of device switching losses, conduction losses and thermal behavior within PLECS multidomain simulations. These models support system level analysis by linking electrical performance with thermal effects during converter and system design.

Relevant links: microchip.com/plecs

MPLAB® Mindi™ SPICE Circuit Simulation Model



PLECS Simulation Model for 30 kW Vienna PFC





Training

If additional training interests you, Microchip offers several resources including in-depth technical training and reference material, self-paced tutorials and significant online resources.

Overview of Technical Training Resources:
www.microchip.com/training

Microchip University:
www.microchip.com/mu

Developer Help Website:
www.microchip.com/developerhelp

Technical Training Centers:
www.microchip.com/seminars

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Elektronik komponent tedarikinde Entegreci

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Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

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Ürün kategorileri

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